# **IBIS**

# (I/O Buffer Information Specification)

Version 3.2

Ratified January 15, 1999

\_\_\_\_\_ \_\_\_\_\_ I/O Buffer Information Specification (IBIS) Version 3.2 (January 15, 1999) IBIS is a standard for electronic behavioral specifications of integrated circuit input/output analog characteristics. \_\_\_\_\_ \_\_\_\_\_ ТАВЬЕ ΟF CONTENTS \_\_\_\_\_ \_\_\_\_\_ Section 1 .... GENERAL INTRODUCTION Section 2 .... STATEMENT OF INTENT Section 3 .... GENERAL SYNTAX RULES AND GUIDELINES Section 4 .... FILE HEADER INFORMATION Section 5 .... COMPONENT DESCRIPTION Section 6 .... MODEL STATEMENT Section 6a ... ADD SUBMODEL DESCRIPTION Section 7 .... PACKAGE MODELING Section 8 .... ELECTRICAL BOARD DESCRIPTION Section 9 .... NOTES ON DATA DERIVATION METHOD \_\_\_\_\_ Keywords: [Date], [Source], [Notes], [Disclaimer], [Copyright]......10 Keyword: [Manufacturer]......11 Keyword: [Pin Mapping]......13 Keyword: [Series Pin Mapping]......16 

	Keyword:	[POWER Clamp Reference]	
		[GND Clamp Reference]	
	Keywords:	[TTgnd], [TTpower]	
	Keywords:	[Pulldown], [Pullup], [GND Clamp], [POWER Clamp]	
	Keywords:	[Rgnd], [Rpower], [Rac], [Cac]	
	Keywords:	[On], [Off]	
	Keywords:	[R Series], [L Series], [Rl Series], [C Series], [Lc Series],	
		Series]	
		[Series Current]	
	Keyword:	[Series MOSFET]	
		[Ramp]	
	Keywords:	[Rising Waveform], [Falling Waveform]	
Se	ction 6a		
	Keyword:	[Submodel]	
		[Submodel Spec]	
		[GND Pulse Table], [POWER Pulse Table]	
Se			
	Keyword:	[Define Package Model]	
	Keyword:	[Manufacturer]	
	Keyword:	[OEM]	
	Keyword:	[Description]	
	Keyword:	[Number Of Sections]	
	Keyword:	[Number Of Pins]	
	Keyword:	[Pin Numbers]	
	Keyword:	[Model Data]	
		[End Model Data]	
		[Resistance Matrix], [Inductance Matrix], [Capacitance Matrix]	
		[Row]	
		[Bandwidth]	
		[End Package Model]	
Se			
		[Begin Board Description]	
		[Manufacturer]	
		[Number Of Pins]	
		[Pin List]	
		[Path Description]	
		[Reference Designator Map]	
	Keyword:	[End Board Description]	
	Keyword:	[End]	
Se			
		es for CMOS models:	
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### **Section 1**

GENERAL INTRODUCTION

This section gives a general overview of the remainder of this document.

Sections 2 and 3 contain general information about the IBIS versions and the general rules and guidelines. Several progressions of IBIS documents are referenced in Section 2 and in the discussion below. They are IBIS Version 1.1 (ratified August, 1993), IBIS Version 2.1 (ratified as ANSI/EIA-656 in January, 1995), and IBIS Version 3.2 (this document ratified in January, 1999).

The functionality of IBIS follows in Sections 4 through 8. Sections 4 through 6 describe the format of the core functionality of IBIS Version 1.1 and the extensions in later versions. The data in these sections are contained in .ibs files. Section 7 describes the package model format of IBIS Version 2.1 and a subsequent extension. Package models can be formatted within .ibs files or can be formatted (along with the Section 4 file header keywords) as .pkg files. Section 8 contains the Electrical Board Description format of IBIS Version 3.2. Along with Section 4 header information, electrical board descriptions must be described in separate .ebd files.

Section 9 contains some notes regarding the extraction conditions and data requirements for IBIS files. This section focuses on implementation conditions based on measurement or simulation for gathering the IBIS compliant data.

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#### Section 2

STATEMENT OF INTENT

In order to enable an industry standard method to electronically transport IBIS Modeling Data between semiconductor vendors, simulation vendors, and end customers, this template is proposed. The intention of this template is to specify a consistent format that can be parsed by software, allowing simulation vendors to derive models compatible with their own products.

One goal of this template is to represent the current state of IBIS data, while allowing a growth path to more complex models / methods (when deemed appropriate). This would be accomplished by a revision of the base template, and possibly the addition of new keywords or categories.

Another goal of this template is to ensure that it is simple enough for semiconductor vendors and customers to use and modify, while ensuring that it is rigid enough for simulation vendors to write reliable parsers.

Finally, this template is meant to contain a complete description of the I/O elements on an entire component. Consequently, several models will need to be defined in each file, as well as a table that equates the appropriate buffer to the correct pin and signal name.

Version 3.2 of this electronic template was finalized by an industry-wide group of experts representing various companies and interests. Regular "EIA IBIS Open Forum" meetings were held to accomplish this task.

Commitment to Backward Compatibility. Version 1.0 is the first valid IBIS ASCII file format. It represents the minimum amount of I/O buffer information required to create an accurate IBIS model of common CMOS and bipolar I/O structures. Future revisions of the ASCII file will add items considered to be "enhancements" to Version 1.0 to allow accurate modeling of new, or other I/O buffer structures. Consequently, all future revisions will be considered supersets of Version 1.0, allowing backward compatibility. In addition, as modeling platforms develop support for revisions of the IBIS ASCII template, all previous revisions of the template must also be supported.

Version 1.1 update. The file "ver1\_1.ibs" is conceptually the same as the 1.0 version of the IBIS ASCII format (ver1\_0.ibs). However, various comments have been added for further clarification.

Version 2.0 update. The file "ver2\_0.ibs" maintains backward compatibility with Versions 1.0 and 1.1. All new keywords and elements added in Version 2.0 are optional. A complete list of changes to the specification is in the IBIS Version 2.0 Release Notes document ("ver2\_0.rn").

Version 2.1 update. The file "ver2\_1.ibs" contains clarification text changes, corrections, and two additional waveform parameters beyond Version 2.0.

Version 3.0 update. The file "ver3\_0.ibs" adds a number of new keywords and functionality. A complete list of functions can be found on eda.org under /pub/ibis/birds/birddir.txt showing the approved Buffer Issue Resolution Documents (BIRDs) that have been approved for Version 3.0.

Version 3.1 update. The file "ver3\_1.ibs" contains a major reformatting of the document and a simplification of the wording. It also contains some new technical enhancements that were unresolved when Version 3.0 was approved.

Version 3.2 update. The file "ver3\_2.ibs" adds ten BIRDs as additions to Version 3.1.

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#### **Section 3**

RULES AND GENERAL SYNTAX GUIDELINES This section contains general syntax rules and guidelines for ASCII IBIS files: 1) The content of the files is case sensitive, except for reserved words and keywords. File names must be all lower case. 2) The following words are reserved words and must not be used for any other purposes in the document: POWER - reserved model name, used with power supply pins, GND - reserved model name, used with ground pins, NC - reserved model name, used with no-connect pins, NA - used where data not available. 3) File names used in the IBIS file must only have lower case characters to enhance UNIX compatibility. File names should have a basename of no more than twenty characters followed by a period, followed by a file name extension of no more than three characters. File names must not contain characters that are illegal in DOS. 4) A line of the file may have at most 80 characters, followed by a line termination sequence. The line termination sequence must be one of the following two sequences: a linefeed character, or a carriage return followed by linefeed character. 5) Anything following the comment character is ignored and considered a comment on that line. The default "|" (pipe) character can be changed by the keyword [Comment Char] to any other character. The [Comment Char] keyword can be used throughout the file as desired. 6) Keywords must be enclosed in square brackets, [], and must start in column 1 of the line. 7) Underscores and spaces are equivalent in keywords. Spaces are not allowed in subparameter names. 8) Valid scaling factors are: n = nano T = tera k = kilo G = giga m = milli p = pico M = mega u = micro f = femtoWhen no scaling factors are specified, the appropriate base units are assumed. (These are volts, amperes, ohms, farads, henries, and seconds.) The parser looks at only one alphabetic character after a numerical entry, therefore it is enough to use only the prefixes to scale the parameters. However, for clarity, it is allowed to use full abbreviations for the units, (e.g., pF, nH, mA, mOhm). In addition, scientific notation IS allowed (e.g., 1.2345e-12).

- 9) The V/I data tables should use enough data points around sharply curved areas of the V/I curves to describe the curvature accurately. In linear regions there is no need to define unnecessary data points.
- 10) The use of TAB characters is legal, but they should be avoided as much as possible. This is to eliminate possible complications that might arise in situations when TAB characters are automatically converted to multiple spaces by text editing, file transferring and similar software. In cases like that, lines might become longer than 80 characters, which is illegal in IBIS files.
- 11) Currents are considered positive when their direction is into the component.
- 12) All temperatures are represented in degrees Celsius.
- 13) Important supplemental information is contained in the last section, "NOTES ON DATA DERIVATION METHOD", concerning how data values are derived.
- 14) Only ASCII characters, as defined in ANSI Standard X3.4-1986, may be used in an IBIS file. The use of characters with codes greater than hexadecimal 07F is not allowed. Also, ASCII control characters (those numerically less than hexadecimal 20) are not allowed, except for tabs or in a line termination sequence. As mentioned in item 10 above, the use of tab characters is discouraged.

Section 4 FILE HEADER INFORMATION Keyword: [IBIS Ver] Required: Yes Description: Specifies the IBIS template version. This keyword informs electronic parsers of the kinds of data types that are present in the file. Usage Rules: [IBIS Ver] must be the first keyword in any IBIS file. It is normally on the first line of the file, but can be preceded by comment lines that must begin with a "|". 3.2 [IBIS Ver] Used for template variations Keyword: [Comment Char] Required: No Description: Defines a new comment character to replace the default "|" (pipe) character, if desired. Usage Rules: The new comment character to be defined must be followed by the underscore character and the letters "char". For example: "|\_char" redundantly redefines the comment character to be the pipe character. The new comment character is in effect only following the [Comment Char] keyword. The following characters MAY NOT be used: A B C D E F G H I J K L M N O P QRSTUVWXYZabcdefghijklmnopqrstu vwxyz0123456789[].\_/=+-Other Notes: The [Comment Char] keyword can be used throughout the file, as desired. \_\_\_\_\_ \_\_\_\_\_ [Comment Char] |\_char Keyword: [File Name] Required: Yes Description: Specifies the name of the IBIS file. Usage Rules: The file name must not be longer than 24 characters (including the extension). The file name must not use characters that are illegal in DOS. In addition, the file name must be all lower case, and use the extension ".ibs". The file name must be the actual name of the file. \_\_\_\_\_ ver3\_2.ibs [File Name] \_\_\_\_\_ Keyword: [File Rev] Required: Yes Description: Tracks the revision level of a particular .ibs file. Usage Rules: Revision level is set at the discretion of the engineer defining the file. The following guidelines are recommended: 0.x silicon and file in development 1.x pre-silicon file data from silicon model only

file correlated to actual silicon measurements 2.x 3.x mature product, no more changes likely \_\_\_\_\_ [File Rev] 1.0 Used for .ibs file variations Keywords: [Date], [Source], [Notes], [Disclaimer], [Copyright] Required: No Description: Optionally clarifies the file. Usage Rules: The keyword arguments can contain blanks, and be of any format. The [Date] keyword argument is limited to a maximum of 40 characters, and the month should be spelled out for clarity. Because IBIS model writers may consider the information in these keywords essential to users, and sometimes legally required, design automation tools should make this information available. Derivative models should include this text verbatim. Any text following the [Copyright] keyword must be included in any derivative models verbatim. \_\_\_\_\_ January 15, 1999 The latest file revision date [Date] Put originator and the source of information here. For [Source] example: From silicon level SPICE model at Intel. From lab measurement at IEI. Compiled from manufacturer's data book at Quad Design, etc. Use this section for any special notes related to the file. [Notes] This information is for modeling purposes only, and is not [Disclaimer] guaranteed. | May vary by component Copyright 1999, XYZ Corp., All Rights Reserved [Copyright]  \_\_\_\_\_

# **Section 5**

DESCRIPTION COMPONENT \_\_\_\_\_ Keyword: [Component] Required: Yes Description: Marks the beginning of the IBIS description of the integrated circuit named after the keyword. Sub-Params: Si\_location, Timing\_location Usage Rules: If the .ibs file contains data for more than one component, each section must begin with a new [Component] keyword. The length of the component name must not exceed 40 characters, and blank characters are allowed. NOTE: Blank characters are not recommended due to usability issues. Si\_location and Timing\_location are optional and specify where the Signal Integrity and Timing measurements are made for the component. The default location is at the 'Pin'. However, the 'Die' location is also available for either or and both subparameters. \_\_\_\_\_ 7403398 MC452 [Component] | Optional subparameters to give measurement Si location Pin Timing location Die | location positions Keyword: [Manufacturer] Required: Yes Description: Specifies the manufacturer's name of the component. Usage Rules: The length of the manufacturer's name must not exceed 40 characters (blank characters are allowed, e.g., Texas Instruments). In addition, each manufacturer must use a consistent name in all .ibs files. \_\_\_\_\_ [Manufacturer] Intel Corp. Keyword: [Package] Required: Yes Description: Defines a range of values for the default packaging resistance, inductance, and capacitance of the component pins. Sub-Params: R\_pkg, L\_pkg, C\_pkg Usage Rules: The typical (typ) column must be specified. If data for the other columns are not available, they must be noted with "NA". Other Notes: If RLC parameters are available for individual pins, they can be listed in columns 4-6 under keyword [Pin]. The values listed in the [Pin] description section override the default values defined here. Use the [Package Model] keyword for more complex package descriptions. If defined, the [Package Model]

   				age] keyword. [Package] keywor	rd must		
[Package]							
variable	typ	min	max				
R_pkg	250.Om	225.Om	275.Om				
L_pkg	15.0nH	12.0nH	18.0nH				
C_pkg	18.0pF	15.0pF	20.0pF				
========== Keywor	======================================						
Require							
Descriptio		e component's :	[/O models	to its various e	external		
		signal names.					
Sub-Param		model_name, R_	pin, L_pin,	C_pin			
Usage Rule				ied. The first	column		
				column, signal_			
	gives the dat	a book name for	the signa	l on that pin.	The		
	third column,	model_name, ma	aps a pin t	o a specific I/O	) buffer		
	model or mode	l selector name	e. Each mo	del_name must ha	ave a		
	corresponding	model or model	l selector :	name listed in a	a [Model]		
	or [Model Sel	or [Model Selector] keyword below, unless it is a reserved					
	model name (P	model name (POWER, GND, or NC).					
	- 1 1'						
		Each line must contain either three or six columns. A pin					
		line with three columns only associates the pin's signal and					
		model. Six columns can be used to override the default					
		package values (specified under [Package]) FOR THAT PIN ONLY.					
		When using six columns, the headers R_pin, L_pin, and C_pin					
		must be listed. If "NA" is in columns 4 through 6, the default packaging values must be used. The headers R_pin, L_pin, and C_pin may be listed in any order					
	n_pin, and c_	pin may be its	Lea III ally	order			
	Column length	Column length limits are:					
	[Pin]	[Pin] 5 characters max					
	model_name	model_name 20 characters max					
	signal_nam	e 20 characte	rs max				
	R_pin	9 characte	rs max				
	L_pin	9 characte					
	C_pin	9 characte	rs max				
[Pin] sign	.al_name model	name R_p:	in L_pin	 C_pin			
		Y	— <u>—r</u> —				
1 RASC	# Buffe			2.0pF			
2 RAS1	# Buffe	r2 209	.Om NA	2.5pF			
3 EN1#	Input	1 NA	6.3nH	NA			
4 A0	3-sta	te					
5 D0	I/Ol						
6 RD#	Input	2 310	.0m 3.0nH	2.0pF			
7 WR#	Input	2					
8 A1	I/02						
9 D1	I/02						
10 GND	GND	297	.0m 6.7nH	3.4pF			
		2					
11 RDY#	Input						
11 RDY# 12 GND	GND	2 270	.0m 5.3nH	4.0pF			

-	Vcc3	POWER				
19 20	NC Vac5	NC POWER	226.0m NA	A	1.0pF	
	_					
	guired:	<b>[Package Model]</b> No				
Descri	ption:	Indicates the name component	of the package	model	to be used for the	
	Rules: Notes:	-				
		QS-SMT-cer-8-p:				
Ke	<b>:=====</b> <b>:yword:</b> guired:	[Pin Mapping] No		======		
-	ption:	Used to indicate w			buses a given drive	
Sub-F	arams:	receiver, or termin pulldown_ref, pull				
Usage	Rules:	Each power and ground not exceed 15 chara name. Each pin name previously in the column, pulldown_ray for that pin. Here power bus. The the bus connection. The	und bus is given acters. The fin me must match on [Pin] section of ef, designates t e the term groun ird column pullu he fourth and fin f contain entries us and power bus	n a un: rst co ne of t f the f the gro nd bus up_ref ifth co es, if	ique name that must lumn contains a pin the pin names declard IBIS file. The secon ound bus connections can also mean anothe designates the power olumns gnd_clamp_ref needed, to specify	
		If the [Pin Mapping connections for EV be given.			, then the bus [Pin] section must	

		d for entrie	ner three or five columns. Use the es that are not needed or that y:
		ry label mus	labels are assumed to be connected. It connect to at least one pin whose
			then both the pulldown_ref and or it will be NC.
	in either the p	oulldown_ref ation to any	and buses are designated by entries or pullup_ref columns. There is no column other than through explicit
	the power conne [Model]s. This Clamp] table ar	ection for the s is also the nd the [Rgnd]	the pulldown_ref column contains ne [Pulldown] table for non-ECL type e power connection for the [GND model unless overridden by a .amp_ref column.
	n contains the power connection for c ECL type models, the [Pulldown] ower connection for the [POWER er] model unless overridden by a _clamp_ref column.		
	pulldowr pullup_r gnd_clam	pping]     5       n_ref     15       cef     15       mp_ref     15	characters max characters max characters max characters max characters max
		-	ed, the headings gnd_clamp_ref and ed. Otherwise, these headings can
[Pin Mapping]	pulldown_ref	pullup_ref	gnd_clamp_ref
 1 2 3 4 5 6	GNDBUS1 GNDBUS2 GNDBUS1 GNDBUS2 GNDBUS2 GNDBUS2	PWRBUS1 PWRBUS2 PWRBUS1 PWRBUS2 PWRBUS2 PWRBUS2	Signal pins and their associated ground and power connections GNDCLMP PWRCLAMP GNDCLMP PWRCLAMP NC PWRCLAMP GNDCLMP NC Some possible clamping connections are shown above for illustration
•			purposes
11	GNDBUS1	NC	One set of ground connections.
12	GNDBUS1	NC	NC indicates no connection to
13	GNDBUS1	NC	power bus.
21 22	GNDBUS2 GNDBUS2	NC   NC	Second set of ground connections

23	GNDBUS2	NC	
. 31 32 33	NC NC NC	PWRBUS1 PWRBUS1 PWRBUS1	One set of power connections. NC indicates no connection to ground bus.
41 42 43	NC NC NC	PWRBUS2 PWRBUS2 PWRBUS2	Second set of power connections
. 51 52 	GNDCLMP NC	NC PWRCLMP	Additional power connections   for clamps
Keyword: Required: Description: Sub-Params: Usage Rules:	<pre>voltages, and d inv_pin, vdiff, Enter only diff Pin], contains inv_pin, contai I/O output. Ea previously in t column, vdiff, threshold volta model types. F entry is 0 V. tdelay_typ, tde of the non-inve values can be o If a pin is a d threshold (vdif and Vinl. If vdiff is not</pre>	ifferential tdelay_typ erential pin a non-invert ns the correct ch pin name he [Pin] set contains the ge between por or output of The fourth, lay_min, and rting pins : f either por ifferential f) overrides defined for	, tdelay_min, tdelay_max n pairs. The first column, [Diff ting pin name. The second column, esponding inverting pin name for must match the pin names declared ction of the IBIS file. The third e specified output and differential pins if the pins are Input or I/O nly differential pins, the vdiff fifth, and sixth columns, d tdelay_max, contain launch delays relative to the inverting pins. The
Other Notes:	<pre>the [Model] Pol [Diff Pin] colu column is Inver be used for bot Column length 1 [Diff Pin] inv_pin vdiff tdelay_typ tdelay_min tdelay_max Each line must entered in the</pre>	arity speci: mn is Non-In ting. This h pins. imits are: 5 charact 9 charact 9 charact 9 charact 9 charact 9 charact 9 charact 9 charact	ters max ters max ters max ters max

	tdelay_max column, its value is interpreted as the tdelay_typ value. When using six columns, the headers tdelay_min and tdelay_max must be listed. Entries for the tdelay_min column are based on minimum magnitudes; and tdelay_max column, maximum magnitudes. One entry of vdiff, regardless of its polarity, is used for difference magnitudes.
[Diff Pin] inv	r_pin vdiff tdelay_typ tdelay_min tdelay_max
 3 4 7 8 9 10 16 15 20 19 22 21 	150mV-1ns0ns-2nsInput or I/O pair0V1nsNANAOutput* pin pairNANANANAOutput* pin pair200mV1nsInput or I/O pin pair0VNAOutput* pin pair, tdelay = 0NANAOutput*, tdelay = 0*Could be Input or I/O with vdiff = 0
Keyword: Required: Description: Sub-Params: Usage Rules:	<pre>[Series Pin Mapping] No Used to associate two pins joined by a series model. pin_2, model_name, function_table_group Enter only series pin pairs. The first column, [Series Pin Mapping], contains the series pin for which input impedances are measured. The second column, pin_2, contains the other connection of the series model. Each pin must match the pin names declared previously in the [Pin] section of the IBIS file. The third column, model_name, associates the Series or Series_switch model for the pair of pins in the first two columns. The fourth column, function_table_group, contains an alphanumeric designator string to associate those sets of Series_switch pins that are switched together. Each line must contain either three or four columns. When using four columns, the header function_table_group must be listed. One possible application is to model crossbar switches where the straight through On paths are indicated by one designator and the cross over On paths are indicated by another designator. If the model referenced is a Series model, then the function_table_group entry is omitted.</pre>
Other Notes:	Column length limits are: [Series Pin Mapping] 5 characters max pin_2 5 characters max model_name 20 characters max function_table_group 20 characters max If the model_name is for a non-symmetrical series model, then the order of the pins is important. The [Series Pin Mapping] and pin_2 entries must be in the columns that correspond with Pin 1 and Pin 2 of the referenced model. This mapping covers only the series paths between pins. The package parasitics and any other elements such as additional capacitance or clamping circuitry are defined by the

model\_name that is referenced in the [Pin] keyword. The model\_names under the [Pin] keyword that are also referenced by the [Series Pin Mapping] keyword may include any legal model or reserved model except for Series and Series\_switch models. Normally the pins will reference a [Model] whose Model type is 'Terminator'. For example, a Series switch model may contain Terminator models on EACH of the pins to describe both the capacitance on each pin and some clamping circuitry that may exist on each pin. In a similar manner, Input, I/O or Output models may exist on each pin of a Series model that is serving as a differential termination. \_\_\_\_\_ [Series Pin Mapping] pin\_2 model\_name function\_table\_group 2 3 1 | Four independent groups CBTSeries 5 6 2 CBTSeries 9 8 CBTSeries 3 12 11 4 CBTSeries 5 22 23 CBTSeries Straight through path 25 26 CBTSeries 5 26 22 CBTSeries 6 | Cross over path 25 23 CBTSeries 6 33 32 Fixed series No group needed Keyword: [Series Switch Groups] Required: No Description: Used to define allowable switching combinations of series switches described using the names of the groups in the [Series Pin Mapping] keyword function\_table\_group column On, Off Sub-Params: Usage Rules: Each state line contains an allowable configuration. A typical state line will start with 'On' followed by all of the on-state group names or an 'Off' followed by all of the off-state group names. Only one of 'On' or 'Off' is required since the undefined states are presumed to be opposite of the explicitly defined states. The state line is terminated with the slash '/', even if it extends over several lines to fit within the 80 character column width restriction. The group names in the function\_table\_group are used to associate switches whose switching action is synchronized by a common control function. The first line defines the assumed (default) state of the set of series switches. Other sets of states are listed and can be selected through a user interface or through automatic control. \_\_\_\_\_ [Series Switch Groups] | Function Group States On 1 2 3 4 / Default setting is all switched On. Off 1 2 3 4 / | All Off setting. On 1 / Other possible combinations below. On 2 /

On 3 / On 4 / On 1 2 / On 1 3 / On 1 4 / On 2 3 / On 2 4 / On 3 4 / On 1 2 3 / On 1 2 4 / On 1 3 4 / On 2 3 4 / Off 4 / The last four lines above could have been replaced Off 3 / | with these four lines with the same meaning. Off 2 / Off 1 / Crossbar switch straight through connection On 5 / On 6 / Crossbar cross over connection Off 5 6 / Crossbar open switches Keyword: [Model Selector] Required: No. Description: Used to pick a [Model] from a list of [Model]s for a pin which uses a programmable buffer. Usage Rules: A programmable buffer must have an individual [Model] section for each one of its modes used in the .ibs file. The names of these [Model]s must be unique and can be listed under the [Model Selector] keyword and/or pin list. The name of the [Model Selector] keyword must match the corresponding model name listed under the [Pin] or [Series Pin Mapping] keyword and must not contain more than 20 characters. A .ibs file must contain enough [Model Selector] keywords to cover all of the model selector names specified under the [Pin] and [Series Pin Mapping] keywords. The section under the [Model Selector] keyword must have two fields. The two fields must be separated by at least one space or tab character. However, the use of tab characters is not recommended in general. The first field lists the [Model] name (up to 20 characters long). The second field contains a short description of the [Model] shown in the first field. The contents and format of this description is not standardized, however it shall be limited in length so that none of the descriptions exceed the 80-character length of the line that it started on. The purpose of the descriptions is to aid the user of the simulator tool in making intelligent buffer mode selections and it can be used by the simulator tool in a user interface dialog box as the basis of an interactive buffer selection mechanism. The first entry under the [Model Selector] keyword shall be considered the default by the simulator tool for all those pins which call this [Model Selector]. The operation of this selection mechanism implies that a group

of pins which use the same programmable buffer (i.e. model selector name) will be switched together from one [Model] to another. Therefore, if two groups of pins, for example an address bus and a data bus, use the same programmable buffer, and the user must have the capability to configure them independently, one can use two [Model Selector] keywords with unique names and the same list of [Model] keywords; however, the usage of the [Model Selector] is not limited to these examples. Many other combinations are possible. \_\_\_\_\_ \_\_\_\_\_ [Pin] signal\_name model\_name R\_pin L\_pin C\_pin 1 RAS0# Progbuffer1 200.0m 5.0nH 2.0pF 2 EN1# Input1 NA 6.3nH NA 3 A0 3-state 4 D0 Progbuffer2 5 D1 Progbuffer2 320.0m 3.1nH 2.2pF б Progbuffer2 D2 7 RD# Input2 310.0m 3.0nH 2.0pF 18 POWER Vcc3 [Model Selector] Progbuffer1 OUT\_2 2 mA buffer without slew rate control OUT\_4 4 mA buffer without slew rate control OUT\_6 6 mA buffer without slew rate control OUT\_4S 4 mA buffer with slew rate control OUT\_6S 6 mA buffer with slew rate control [Model Selector] Progbuffer2 OUT 2 2 mA buffer without slew rate control 6 mA buffer without slew rate control OUT 6 6 mA buffer with slew rate control OUT 6S OUT 8S 8 mA buffer with slew rate control OUT 10S 10 mA buffer with slew rate control 

# Section 6

STATEMENT MODEL Keyword: [Model] Required: Yes Description: Used to define a model, and its attributes. Sub-Params: Model\_type, Polarity, Enable, Vinl, Vinh, C\_comp, Vmeas, Cref, Rref, Vref Usage Rules: Each model type must begin with the keyword [Model]. The The model name must match the one that is listed under [Pin], [Model Selector] or [Series Pin Mapping] keyword and must not contain more than 20 characters. A .ibs file must contain enough [Model] keywords to cover all of the model names specified under the [Pin], [Model Selector] and [Series Pin Mapping] keywords, except for those model names that use reserved words (POWER, GND and NC). Model names with reserved words are an exception and they do not have to have a corresponding [Model] keyword. Model\_type must be one of the following: Input, Output, I/O, 3-state, Open\_drain, I/O\_open\_drain, Open\_sink, I/O\_open\_sink, Open\_source, I/O\_open\_source, Input\_ECL, Output\_ECL, I/O\_ECL, 3-state\_ECL, Terminator, Series, and Series\_switch. Special usage rules apply to the following. Some definitions are included for clarification: Input These model types must have Vinl and Vinh defined. If they are not defined, the I/O I/O\_open\_drain parser issues a warning and the default values of Vinl = 0.8 V and Vinh = 2.0 V are I/O open sink I/O\_open\_source assumed. Input ECL These model types must have Vinl and Vinh I/O\_ECL defined. If they are not defined, the parser issues a warning and the default values of Vinl = -1.475 V and Vinh = -1.165 V are assumed. Terminator This model type is an input-only model that can have analog loading effects on the circuit being simulated but has no digital logic thresholds. Examples of Terminators are: capacitors, termination diodes, and pullup resistors. Output This model type indicates that an output always sources and/or sinks current and

cannot be disabled.

- 3-state This model type indicates that an output can be disabled, i.e. put into a high impedance state.
- Open\_sink These model types indicate that the output Open\_drain has an OPEN side (do not use the [Pullup] keyword, or if it must be used, set I = 0 mA for all voltages specified) and the output SINKS current. Open\_drain model type is retained for backward compatibility.
- Open\_source This model type indicates that the output has an OPEN side (do not use the [Pulldown] keyword, or if it must be used, set I = 0 mA for all voltages specified) and the output SOURCES current.
  - Input\_ECLThese model types specify that the modelOutput\_ECLrepresents an ECL type logic that followsI/O\_ECLdifferent conventions for the [Pulldown]3-state\_ECLkeyword.
- Series This model type is for series models that can be described by [R Series], [L Series], [Rl Series], [C Series], [Lc Series], [Rc Series], [Series Current] and [Series MOSFET] keywords
- Series\_switch This model type is for series switch models that can be described by [On], [Off], [R Series], [L Series], [Rl Series], [C Series], [Lc Series], [Rc Series], [Series Current] and [Series MOSFET] keywords

The Model\_type and C\_comp subparameters are required. The Polarity, Enable, Vinl, Vinh, Vmeas, Cref, Rref, and Vref subparameters are optional. C\_comp defines the silicon die capacitance. This value should not include the capacitance of the package. C\_comp is allowed to use "NA" for the min and max values only. The Polarity subparameter can be defined as either Non-Inverting or Inverting, and the Enable subparameter can be defined as either Active-High or Active-Low.

The Cref and Rref subparameters correspond to the test load that the semiconductor vendor uses when specifying the propagation delay and/or output switching time of the model. The Vmeas subparameter is the reference voltage level that the semiconductor vendor uses for the model. Include Cref, Rref, Vref, and Vmeas information to facilitate board-level timing simulation. The assumed connections for Cref, Rref, and Vref are shown in the following diagram:

Rref Driver --o---/\/\/\----o Vref === Cref GND Other Notes: A complete [Model] description normally contains the following keywords: [Voltage Range], [Pullup], [Pulldown], [GND Clamp], [POWER Clamp], and [Ramp]. A Terminator model uses one or more of the [Rgnd], [Rpower], [Rac], and [Cac]. However, some models may have only a subset of these keywords. For example, an input structure normally only needs the [Voltage Range], [GND Clamp], and possibly the [POWER Clamp] keywords. If one or more of [Rgnd], [Rpower], [Rac], and [Cac] keywords are used, then the Model\_type must be Terminator. \_\_\_\_\_ CLK1, CLK2,... | Optional signal list, if desired Signals [Model] Clockbuffer Model type I/O Non-Inverting Polarity Enable Active-High Vinl = 0.8Vinput logic "low" DC voltage, if any Vinh = 2.0V| input logic "high" DC voltage, if any Vmeas = 1.5VReference voltage for timing measurements Cref = 50pFTiming specification test load capacitance value Rref = 500Timing specification test load resistance value Vref = 0Timing specification test load voltage variable min max typ 12.0pF 10.0pF 15.0pF C comp \_\_\_\_\_ Keyword: [Model Spec] Required: No Sub-Params: Vinh, Vinl, Vinh+, Vinh-, Vinl+, Vinl-, S\_overshoot\_high, S\_overshoot\_low, D\_overshoot\_high, D\_overshoot\_low, D\_overshoot\_time, Pulse\_high, Pulse\_low, Pulse\_time, Vmeas Description: The [Model Spec] keyword defines four columns under which specification subparameters are defined. The following subparameters are defined: Vinh Input voltage threshold high Vinl Input voltage threshold low Hysteresis threshold high max Vt+ Vinh+ Hysteresis threshold high min Vt+ Vinh-Vinl+ Hysteresis threshold low max Vt-Vinl-Hysteresis threshold low min Vt-S\_overshoot\_high Static overshoot high voltage S overshoot low Static overshoot low voltage D overshoot high Dynamic overshoot high voltage D overshoot low Dynamic overshoot low voltage D\_overshoot\_time Dynamic overshoot time Pulse immunity high voltage Pulse\_high

Pulse_low	Pulse immunity low voltage
Pulse_time	Pulse immunity time
Vmeas	Measurement voltage for timing measurements

Usage Rules: [Model Spec] must follow all other subparameters under the [Model] keyword.

For each subparameter contained in the first column, the remaining three hold its typical, minimum and maximum values. The entries of typical, minimum and maximum must be placed on a single line and must be separated by at least one white space or tab character. All four columns are required under the [Model Spec] keyword. However, data is required only in the typical column. If minimum and/or maximum values are not available, the reserved word "NA" must be used indicating the typical value by default.

The minimum and maximum values are used for specifications subparameter values that may track the min and max operation conditions of the [Model]. Usually it is related to the Voltage Range settings.

Unless noted below, each subparameter does not require having any other subparameter.

Vinh, Vinl rules:

The threshold subparameter lines provide additional min and max column values, if needed. The typ column values are still required and would be expected to override the Vinh and Vinl subparameter values specified elsewhere. Note: the syntax rule that require inserting Vinh and Vinl under models remains unchanged even if the values are defined under the [Model Spec] keyword.

To mimic a hysteresis effect, the values of Vinh and Vinl may be interchanged such that the Vinl value is larger than the Vinh value. However, simulators may process this information differently or report an error.

Vinh+, Vinh-, Vinl+, Vinl- rules:

The four hysteresis subparmeters must all be defined before the hysteresis threshold rules become effective. Otherwise the standard threshold subparameters remain in effect. The hysteresis thresholds shall be at the Vinh+ and Vinh- values for a low-to-high transition, and at the Vinl+ and Vinlvalues for a high-to-low transition.

S\_overshoot\_high, S\_overshoot\_low rules:

The static overshoot subparameters provide the voltage values for which the model is no longer guaranteed to function correctly.

D\_overshoot\_high, D\_overshoot\_low, D\_overshoot\_time rules:

The dynamic overshoot values provide a time window during which the overshoot may exceed the static overshoot limits but be below the dynamic overshoot limits. D\_overshoot\_time is required for dynamic overshoot testing. In addition, if D\_overshoot\_high is specified, then S\_overshoot\_high is necessary for testing beyond the static limit. Similarly, if D\_overshoot\_low is specified, then S\_overshoot\_low is necessary for testing beyond the static limit.

Pulse\_high, Pulse\_low, Pulse\_time rules:

The pulse immunity values provide a time window during which a rising pulse may exceed the nearest threshold value but be below the pulse voltage value and still not cause the input to switch. Pulse\_time is required for pulse immunity testing. A rising response is tested only if Pulse\_high is specified. Similarly, a falling response is tested only if Pulse\_low is specified. The rising response may exceed the Vinl value, but remain below the Pulse\_high value. Similarly, the falling response may drop below the Vinh value, but remain above the Pulse\_low value. In either case the input is regarded as immune to switching if the responses are within these extended windows. If the hysteresis thresholds are defined, then the rising response shall use Vinh- as the reference voltage, and the falling response shall use Vinl+ as the reference voltage.

Vmeas rules:

The Vmeas values under the [Model Spec] keyword override the Vmeas entry elsewhere.

[Model Spec] Subparameter	tum	min	max	
	typ	11111	lliax	
Thresholds				
Vinh	3.5	3.15	3.85	70% of Vcc
Vinl	1.5	1.35	1.65	30% of Vcc
Vinh	3.835	3.335	4.335	Offset from Vcc
Vinl	3.525	3.025	4.025	for PECL
Hysteresis				
Vinh+	2.0	NA	NA	Overrides the
Vinh-	1.6	NA	NA	thresholds
Vinl+	1.1	NA	NA	
Vinl-	0.6	NA	NA	All 4 are required
0vershoot				
	5.5	5.0	6.0	Static overshoot
S_overshoot_low	-0.5	NA	NA	
D_overshoot_high	6.0	5.5	6.5	Dynamic overshoot
D_overshoot_low	-1.0	-1.0	-1.0	requires
				D_overshoot_time

D_overshoot_time		20n	20n	20n	& static overshoot
Pulse Immunity					
 Pulse_high Pulse_low Pulse_time		3V 0 3n	NA NA NA	NA NA NA	Pulse immunity   requires   Pulse_time
Timing Thresh 	olds				
Vmeas   		3.68	3.18	4.68	A 5 volt PECL   example
Keyword: Required: Description: Usage Rules:	The [Add add the f list of s column co contains If the to models, t All. For then the 3-state m submodel The submo type. Fo Open or O Non-Drivi Input, th The [Add Series_sw Refer to	s a submode Submodel] k unctionalit ubmodels in ntains the a submodel p-level mod he submodel example, i submodel is odel. Set is to be us del mode ca r example, utput type, ng. Simila e submodel] k itch model	teyword is i by that is con- each line submodel na- mode under del type is mode may b f the submode sed for all annot confli- if the top- the submode arly, if the mode cannot types.	nvoked wit ontained : that follo me. The s which the one of the pe Driving odel mode : in the high lande to modes of of ct with the level mode top-level be set to not defined	operation. he top-level model el type is an annot be set to l model type is
[Add Submodel]   Submodel_name Mode Bus_Hold_1 Non-Driving   Adds the electrical characterist   [Submodel] Bus_Hold_1 for receiver or   high-Z mode only Dynamic_clamp_1 All   Adds the Dynmanic_clamp_1 model   all modes of operation					receiver or
<b>Keyword:</b> Required: Description: Usage Rules:	[Driver S No Describes models to	<b>chedule]</b> the relati produce a	.ve model sw multi-stage	vitching se d driver.	equence for referenced s a hierarchical order

between models and should be placed under the [Model] which acts as the top-level model. The scheduled models are then referenced from the top-level [Model] by the [Driver Schedule] keyword.

The [Driver Schedule] table consists of five columns. The first column contains the model names of other models that exists in the .ibs file. The remaining four columns describe delays: Rise\_on\_dly, Rise\_off\_dly, Fall\_on\_dly, and Falling\_off\_dly. All values are referenced to 0 seconds for the start of the rising transition and 0 seconds for the start of the falling transition. All delays must be equal to or greater than 0.

The Rise\_on\_dly entry gives the beginning of the low-to-high transition. The Rise\_off\_dly entry may be given to end the low-to-high transition and initiate a high-to-low transition during the rising cycle. Similarly, the Fall\_on\_dly gives the beginning of the high-to-low transition. The Fall\_off\_dly may be given to end the high-to-low transition and initiate a low-to-high transition.

Use 'NA' when no transition is applicable. For each model, the transition sequence must be complete, i.e., it must start and end at the same state.

Only the [Pulldown] and [Pullup] tables and transition data [Ramp] or [Rising Waveform] and [Falling Waveform] data are used from each model that is referenced. The [Model] keyword provides the specification information, [GND Clamp] and [POWER Clamp], and C\_comp, regardless of information contained in the referenced models.

It is recommended that a "golden waveform" for the device consisting of a [Rising Waveform] table and a [Falling Waveform] table be supplied under the [Model] keyword to serve as a reference for validation.

No [Driver Schedule] may reference a model which itself has within it a [Driver Schedule] table keyword.

Other Notes: The added models typically consist of Open\_sink (Open\_drain) or Open\_source models to provide sequentially increased drive strengths. The added drive may be removed within the same transition for a momentary boost or during the opposite transition.

The syntax also allows for reducing the drive strength.

Note that the Rise\_on\_dly, Rise\_off\_dly, Fall\_on\_dly, Fall\_off\_dly parameters are single value parameters, so typical, minimum and maximum conditions cannot be described with them directly. In order to account for those effects, one can refer to the fastest waveform table with the delay number and then insert an appropriate amount of horizontal lead in section in those waveforms which need more delay.

Note: In a future release, the [Driver Schedule] keyword may be replaced by a newer method of specification that is consistent with some other planned extensions. However, the [Driver Schedule] syntax will continue to be supported. \_\_\_\_\_ [Driver Schedule] Model name Rise\_on\_dly Rise\_off\_dly Fall\_on\_dly Fall\_off\_dly MODEL\_OUT NA 0.0ns 0.0nsNA Examples of added multi-staged transitions NA M\_O\_SOURCE1 0.5ns 0.5ns NA low (high-Z) to highhigh to low (high-Z)0.5n1.5nNAlow to high to lowlow (high-Z)1.0nNA1.5n M O SOURCE2 0.5n 1.5n M\_O\_DRAIN1 high (high-Z) to low low to high (high-Z) M O DRAIN2 NA NA 1.5n 2.0n high to low to high high (high-Z) Keyword: [Temperature Range] Required: Yes, if other than the preferred 0, 50, 100 degree Celsius range Description: Defines the temperature range over which the model is to operate. Usage Rules: List the actual die temperatures (not percentages) in the typ, min, max format. "NA" is allowed for min and max only. Other Notes: The [Temperature Range] keyword also describes the temperature range over which the various V/I tables and ramp rates were derived. \_\_\_\_\_ min variable typ max [Temperature Range] 27.0 -50 130.0 \_\_\_\_\_ Keyword: [Voltage Range] Required: Yes, if [Pullup Reference], [Pulldown Reference], [POWER Clamp Reference], and [GND Clamp Reference] are not present Description: Defines the power supply voltage tolerance over which the model is intended to operate. It also specifies the default voltage rail to which the [Pullup] and [POWER Clamp] V/I data is referenced. Usage Rules: Provide actual voltages (not percentages) in the typ, min, max format. "NA" is allowed for the min and max values only. Other Notes: If the [Voltage Range] keyword is not present, then all four of the keywords described below must be present: [Pullup Reference], [Pulldown Reference], [POWER Clamp Reference], and [GND Clamp Reference]. If the [Voltage Range] is present, the other keywords are optional and may or may not be used as required. It is legal (although redundant) for an optional keyword to specify the same voltage as specified by the [Voltage Range] keyword. \_\_\_\_\_ variable min typ max [Voltage Range] 5.0V 4.5V 5.5V 

Keyword: [Pullup Reference] Required: Yes, if the [Voltage Range] keyword is not present. Description: Defines a voltage rail other than that defined by the [Voltage Range] keyword as the reference voltage for the [Pullup] V/I data. Usage Rules: Provide actual voltages (not percentages) in the typ, min, max format. "NA" is allowed for the min and max values only. Other Notes: This keyword, if present, also defines the voltage range over which the typ, min, and max  $dV/dt_r$  values are derived. \_\_\_\_\_ variable min typ max [Pullup Reference] 5.0V 4.5V 5.5V \_\_\_\_\_ Keyword: [Pulldown Reference] Required: Yes, if the [Voltage Range] keyword is not present. Description: Defines a power supply rail other than 0 V as the reference voltage for the [Pulldown] V/I data. If this keyword is not present, the voltage data points in the [Pulldown] V/I table are referenced to 0 V. Usage Rules: Provide actual voltages (not percentages) in the typ, min, max format. "NA" is allowed for the min and max values only. Other Notes: This keyword, if present, also defines the voltage range over which the typ, min, and max dV/dt\_f values are derived. \_\_\_\_\_ variable typ min max [Pulldown Reference] 0V 0V 0V Keyword: [POWER Clamp Reference] Required: Yes, if the [Voltage Range] keyword is not present. Description: Defines a voltage rail other than that defined by the [Voltage Range] keyword as the reference voltage for the [POWER Clamp] V/I data. Usage Rules: Provide actual voltages (not percentages) in the typ, min, max format. "NA" is allowed for the min and max values only. Other Notes: Refer to the "Other Notes" section of the [GND Clamp Reference] keyword. \_\_\_\_\_ typ variable min max POWER Clamp Reference] 5.0V 4.5V 5.5V \_\_\_\_\_ Keyword: [GND Clamp Reference] Required: Yes, if the [Voltage Range] keyword is not present. Description: Defines a power supply rail other than 0 V as the reference voltage for the [GND Clamp] V/I data. If this keyword is not present, the voltage data points in the [GND Clamp] V/I table are referenced to 0 V. Usage Rules: Provide actual voltages (not percentages) in the typ, min, max format. "NA" is allowed for the min and max values only. Other Notes: Power Supplies: It is intended that standard TTL and CMOS models be specified using only the [Voltage Range] keyword. However, in cases where the output characteristics of a model depend on more than a single supply and ground, or a [Pullup], [Pulldown], [POWER Clamp], or [GND Clamp] table is referenced to something other than the default supplies, use the

variable GND Clamp Refe	ty erence] 0V	-	nin )V	max OV
<b>Keywords:</b> Required: Description:	[TTgnd], [ No These keywa estimate th	<b>TTpower]</b> ords specify th he transit time	e capacitanc	ime parameters used to es or develop transit tin mp] and [POWER Clamp]
Usage Rules:	For each or values corr Clamp] or TT(typ), T and must be character. keywords. column. I:	responding to t [POWER Clamp] t [(min), and TT e separated by All three co However, data f minimum and/c ed word "NA" mu	the typical, tables, resp (max) must b at least on tumns are re is required or maximum v	e columns hold the transi minimum and maximum [GNI pectively. The entries for be placed on a single line white space or tab equired under these I only in the typical values are not available, indicating the TT(typ)
Other Notes:	The transis Spice reference d(Id)/d(Vd operating ) This exprese resistance practice. voltage (Vo where Is is Boltzmann's Then d(Id)) is conduct simplification the [GND C correspond value. If	t time capacita rence model as ) defines the H point of the di ssion does not . Such a resis Assume that th d) relationship s the saturations /d(Vd) is appro- tion Ct = TT * lamp] and [POWH ing TTgnd or TT the [Temperatu he default "typ	Ct = TT * d CC conductant lode, and TT include any stance is as he internal o is Id = Is on current, d T is tempe oximately (q otherwise. (q/kT) * Id CR Clamp] op Spower is us are Range] k	ed to C_comp. It is in a l(Id)/d(Vd) where ace at the incremental DC r is the transit time. r internal series sumed to be negligible in diode current (Id) - s * (exp(q(Vd)/kT) - 1) q is electron charge, k is erature in degrees Kelvin. [/kT) * Id when the diode This yields the l. The Id is found from berating points, and the sed to calculate the Ct seyword is not defined, are for all Ct
	the effects	s. They may be diode equations	e different s. Refer to	re intended to APPROXIMATE from the values found in the NOTES ON DATA e effective values.
variable TTgnd] TTpower]	TT(typ) 10n 12n	TT(min) 12n NA	TT (m 9n NA	
Keywords:	[Pulldown] Yes, if the The data pe the pulldow V/I tables	, [Pullup], [G ey exist in the pints under the wn and pullup s of the clampin	<b>TD Clamp], [</b> e model ese keywords structures c ng diodes co	<b>POWER Clamp]</b> s define the V/I tables of of an output buffer and the onnected to the GND and the are considered positive

when their direction is into the component. Usage Rules: In each of these sections, the first column contains the voltage value, and the three remaining columns hold the typical, minimum, and maximum current values. The four entries, Voltage, I(typ), I(min), and I(max) must be placed on a single line and must be separated by at least one white space or tab character.

All four columns are required under these keywords. However, data is only required in the typical column. If minimum and/or maximum current values are not available, the reserved word "NA" must be used. "NA" can be used for currents in the typical column, but numeric values MUST be specified for the first and last voltage points on any V/I table. Each V/I table must have at least 2, but not more than 100, voltage points.

Other Notes: The V/I table of the [Pullup] and the [POWER Clamp] structures are 'Vcc relative', meaning that the voltage values are referenced to the Vcc pin. (Note: Under these keywords, all references to 'Vcc' refer to the voltage rail defined by the [Voltage Range], [Pullup Reference], or [POWER Clamp Reference] keywords, as appropriate.) The voltages in the data tables are derived from the equation: Vtable = Vcc -Voutput.

> Therefore, for a 5 V model, -5 V in the table actually means 5 V above Vcc, which is +10 V with respect to ground; and 10 V means 10 V below Vcc, which is -5 V with respect to ground. Vcc-relative data is necessary to model a pullup structure properly, since the output current of a pullup structure depends on the voltage between the output and Vcc pins and not the voltage between the output and ground pins. Note that the [GND Clamp] V/I table can include quiescent input currents, or the currents of a 3-stated output, if so desired.

When tabulating data for ECL models, the data in the [Pulldown] table is measured with the output in the 'logic low' state. In other words, the data in the table represents the V/I characteristics of the output when the output is at the most negative of its two logic levels. Likewise, the data in the [Pullup] table is measured with the output in the 'logic one' state and represents the V/I characteristics when the output is at the most positive logic level. Note that in BOTH of these cases, the data is referenced to the Vcc supply voltage, using the equation: Vtable = Vcc - Voutput.

Monotonicity Requirements:

To be monotonic, the V/I table data must meet any one of the following 8 criteria:

- 1- The CURRENT axis either increases or remains constant as the voltage axis is increased.
- 2- The CURRENT axis either increases or remains constant as the voltage axis is decreased.
- 3- The CURRENT axis either decreases or remains constant as

the voltage axis is increased.

- 4- The CURRENT axis either decreases or remains constant as the voltage axis is decreased.
- 5- The VOLTAGE axis either increases or remains constant as the current axis is increased.
- 6- The VOLTAGE axis either increases or remains constant as the current axis is decreased.
- 7- The VOLTAGE axis either decreases or remains constant as the current axis is increased.
- 8- The VOLTAGE axis either decreases or remains constant as the current axis is decreased.

An IBIS syntax checking program shall test for non-monotonic data and provide a maximum of one note per V/I table if non-monotonic data is found. For example:

"NOTE: Line 300, Pulldown V/I table for model DC040403 is non-monotonic! Most simulators will filter this data to remove the non-monotonic data."

It is also recognized that the data may be monotonic if currents from both the output stage and the clamp diode are added together as most simulators do. To limit the complexity of the IBIS Version 2.x and Version 3.x syntax checking programs, such programs will conduct monotonicity testing only on one V/I table at a time.

It is assumed that the simulator sums the clamp tables together with the appropriate [Pullup] or [Pulldown] table when a buffer is driving high or low, respectively. From this assumption and the nature of 3-statable buffers, it follows that the data in the clamping table sections are handled as constantly present tables and the [Pullup] and [Pulldown] tables are used only when needed in the simulation.

The clamp tables of an Input or I/O buffer can be measured directly with a curve tracer, with the I/O buffer 3-stated. However, sweeping enabled buffers results in tables that are the sum of the clamping tables and the output structures. Based on the assumption outlined above, the [Pullup] and [Pulldown] tables of an IBIS model must represent the difference of the 3-stated and the enabled buffer's tables. (Note that the resulting difference table can demonstrate a non-monotonic shape.) This requirement enables the simulator to sum the tables, without the danger of double counting, and arrive at an accurate model in both the 3-stated and enabled conditions.

Since in the case of a non 3-statable buffer, this difference table cannot be generated through lab measurements (because the clamping tables cannot be measured alone), the [Pullup] and [Pulldown] tables of an IBIS model can contain the sum of the clamping characteristics and the output structure. In this case, the clamping tables must contain all zeroes, or the keywords must be omitted.

```
[Pulldown]
  Voltage
            I(typ)
                      I(min)
                               I(max)
                     -34.Om
  -5.0V
           -40.0m
                              -45.0m
           -39.Om
                     -33.Om
  -4.0V
                              -43.0m
    .
   0.0V
             0.Om
                       0.Om
                                0.Om
    .
   5.0V
            40.0m
                      34.0m
                               45.0m
  10.0V
            45.Om
                      40.0m
                               49.Om
[Pullup]
                                     | Note: Vtable = Vcc - Voutput
  Voltage
            I(typ)
                      I(min)
                               I(max)
  -5.0V
            32.Om
                      30.Om
                               35.Om
  -4.0V
            31.Om
                      29.Om
                               33.Om
    .
   0.0V
             0.Om
                       0.Om
                                0.Om
    .
   5.0V
           -32.0m
                     -30.0m
                              -35.0m
  10.0V
           -38.Om
                     -35.Om
                              -40.0m
[GND Clamp]
  Voltage
            I(typ)
                      I(min)
                               I(max)
  -5.0V -3900.0m -3800.0m
                            -4000.0m
  -0.7V
           -80.Om
                    -75.Om
                              -85.Om
  -0.6V
           -22.Om
                     -20.Om
                               -25.0m
  -0.5V
            -2.4m
                     -2.Om
                               -2.9m
             0.Om
                       0.Om
                                0.Om
  -0.4V
             0.Om
                       0.Om
                                0.Om
   5.0V
                                      | Note: Vtable = Vcc - Voutput
[POWER Clamp]
  Voltage
                      I(min)
                               I(max)
            I(typ)
          4450.0m
  -5.0V
                        NA
                                 NA
  -0.7V
            95.Om
                        NA
                                 NA
  -0.6V
            23.Om
                        NA
                                 NA
  -0.5V
             2.4m
                        NA
                                 NA
  -0.4V
             0.Om
                                 NA
                        NA
   0.0V
             0.Om
                        NA
                                 NA
[Rgnd], [Rpower], [Rac], [Cac]
    Keywords:
               Yes, if they exist in the model
    Required:
 Description:
               The data for these keywords define the resistance values of
               Rgnd and Rpower connected to GND and the POWER pins,
               respectively, and the resistance and capacitance values for an
               AC terminator.
 Usage Rules: For each of these keywords, the three columns hold the
```



power and ground net descriptions. \_\_\_\_\_ variableR(typ)R(min)Rgnd]330ohm300ohmRpower]220ohm200ohm R(max) [Rqnd] 360ohm | Parallel Terminator NA [Rpower] [Rac] 30ohm NA NA C(typ) | AC terminator variable C(min) C(max) [Cac] 50pF NA NΑ \_\_\_\_\_ Keywords: [On], [Off] Required: Yes, both [On] and [Off] for Series\_switch Model\_types only Description: The 'On' state electrical models are positioned under [On]. The 'Off' state electrical models are positioned under [Off]. Usage Rules: These keywords are only valid for Series\_switch Model\_types. Only keywords associated with Series\_switch electrical models are permitted under [On] or [Off]. The Series electrical models describe the path for one state only and do not use the [On] and [Off] keywords. In Series\_switch models, [On] or [Off] must be positioned before any of the [R Series], [L Series], Rl Series], [C Series], [Lc Series], [Rc Series], [Series Current], and [Series MOSFET] keywords. There is no provision for any of these keywords to be defined once, but to apply to both states. \_\_\_\_\_ [On] ... On state keywords such as [R Series], [Series Current], [Series MOSFET] [Off] ... Off state keywords such as [R Series], [Series Current] \_\_\_\_\_ Keywords: [R Series], [L Series], [Rl Series], [C Series], [Lc Series], [Rc Series] Required: Yes, if they exist in the model Description: The data for these keywords allow the definition of Series or Series\_switch R, L or C paths. Usage Rules: For each of these keywords, the three columns hold the typical, minimum, and maximum resistance values. The three entries must be placed on a single line and must be separated by at least one white space or tab character. All three columns are required under these keywords. However, data is only required in the typical column. If minimum and/or maximum values are not available, the reserved word "NA" must be used. Other Notes: This series RLC model is defined to allow IBIS to model simple passive models and/or parasitics. These keywords are valid only for Series or Series\_switch Model types. The model is:

R Series +---/\/\/\/\----+ Pin 1 | L Series Rl Series | Pin 2 <----/\/\/\/\/\---------@@@@@@@@\_---/\/\/\/\---+ Lc Series Rc Series C Series [Rl Series] shall be defined only if [L Series] exists. [Rl Series] is 0 ohms if it is not defined in the path. [Rc Series] and [Lc Series] shall be defined only if [C Series] exists. [Rc Series] is 0 ohms if it is not defined in the path. [Lc Series is 0 henries if it is not defined in the path. C\_comp values are ignored for these keywords. \_\_\_\_\_ variable R(typ) R(min) R(max) 60hm 12ohm [R Series] 80hm L(min) variable L(typ) L Series] 5nH L(max) [L Series] NA NA | variable R(typ) [Rl Series] 40hm R(min) NA R(max) NA NA variable C(typ) C(min) C(max) | The other elements [C Series] | are 0 impedance 50pF NA NA \_\_\_\_\_\_ Keyword: [Series Current] Required: Yes, if they exist in the model Description: The data points under this keyword define the V/I tables for voltages measured at Pin 1 with respect to Pin 2. Currents are considered positive if they flow into Pin 1. Pins 1 and 2 are listed under the [Series Pin Mapping] keyword under columns [Series Pin Mapping] and pin\_2, respectively. Usage Rules: The first column contains the voltage value, and the remaining columns hold the typical, minimum, and maximum current values. The four entries, Voltage, I(typ), I(min), and I(max) must be placed on a single line and must be separated by at least one white space or tab character. All four columns are required under these keywords. However, data is only required in the typical column. If minimum and/or maximum current values are not available, the reserved word "NA" must be used. "NA" can be used for currents in the typical column, but numeric values MUST be specified for the first and last voltage points on any V/I table. Each V/I table must have at least 2, but not more than 100, voltage points. Other Notes: There is no monotonicity requirement. However the model

supplier should realize that it may not be possible to derive a behavioral model from non-monotonic data. These keywords are valid only for Series or Series\_switch Model types. The model is: Table Current ----> + Table Voltage -Pin 1 |----- Pin 2 <---+ +---> |----| C\_comp values are ignored for [Series Current] models. \_\_\_\_\_ [Series Current] Voltage I(typ) I(min) I(max) -5.0V -3900.0m -3800.0m -4000.0m -0.7V -80.0m -75.0m -85.0m -0.6V -22.0m -20.0m -25.0m -2.4m -2.0m -2.9m -0.5V 0.0m 0.0m -0.4V 0.Om 5.0V 0.Om 0.Om 0.0m Keyword: [Series MOSFET] Required: Yes, for series MOSFET switches Description: The data points under this keyword define the V/I tables for voltages measured at Pin 2 for a given Vds setting. Currents are considered positive if they flow into Pin 1. Pins 1 and 2 are listed under the [Series Pin Mapping] keyword under [Series Pin Mapping] and pin\_2 columns, respectively. Sub-Params: Vds Usage Rules: The first column contains the voltage value, and the three remaining columns hold the typical, minimum, and maximum current values. The four entries, Voltage, I(typ), I(min), and I(max) must be placed on a single line and must be separated by at least one white space or tab character. All four columns are required under these keywords. However, data is only required in the typical column. If minimum and/or maximum current values are not available, the reserved word "NA" must be used. "NA" can be used for currents in the typical column, but numeric values MUST be specified for the first and last voltage points on any V/I table. Each V/I table must have at least 2, but not more than 100, voltage points. Other Notes: There is no monotonicity requirement. However the model supplier should realize that it may not be possible to derive a behavioral model from non-monotonic data. The model is:


Vg = [Voltage Range] = Vcc Vgs = Table Voltage = Vtable = Vcc - Vs Ids = Table Current for a given Vcc and Vds

Internal logic that is generally referenced to the power rail is used to set the MOSFET switch to its 'On' state. Thus the [Voltage Range] settings provide the assumed gate voltages. If the [POWER Clamp Reference] exists, it overrides the [Voltage Range] value. The table entries are actually the Vgs values referenced to the power rail. The polarity conventions are identical with those used for other tables that are referenced to power rails. Thus the voltage column can be viewed as a table defining the source voltages Vs according to the convention: Vtable = Vcc - Vs.

If the switch is used in an application such as interfacing between 3.3 V and 5.0 V logic, the Vcc may be biased at a voltage (such as 4.3 V) that is different from a power rail voltage (such as 5.0 V) used to create the model. Just readjust the [Voltage Range] entries (or [POWER Clamp Reference] entries).

One fundamental assumption in the MOSFET switch model is that it operates in a symmetrical manner. The tables and expressions are given assuming that Vd >= Vs. If Vd < Vs, then apply the same relationships under the assumption that the source and drain nodes are interchanged. A consequence of this assumption is that the Vds subparameter is constrained to values Vds > 0. It is assumed that with Vds = 0 the currents will be 0 mA. A further consequence of this assumption that would be embedded in the analysis process is that the voltage table is based on the side of the model with the lowest voltage (and that side is defined as the source). Thus the analysis must allow current to flow in both directions, as would occur due to reflections when the switch is connected in series with an unterminated transmission line.

The model data is used to create an On state relationship between the actual drain to source current, ids, and the actual drain to source voltage, vds:

ids = f(vds).

This functional relationship depends on the actual source voltage Vs and can be expressed in terms of the corresponding table currents associated with Vs (and expressed as a function of Vgs).

If only one [Series MOSFET] table is supplied (as a first order approximation), the functional relationship is assumed to be linearly related to the table drain to source current, Ids, for the given Vds subparameter value and located at the existing gate to source voltage value Vgs. This table current is denoted as Ids(Vgs, Vds). The functional relationship becomes: ids = Ids(Vgs, Vds) \* vds / Vds. More than one [Series MOSFET] table is permitted, but it is simulator dependent how the data will be used. Each successive [Series MOSFET] table must have a different subparameter value for Vds. The number of tables must not exceed 100. C\_comp values are ignored for [Series MOSFET] models. \_\_\_\_\_ [On] [Series MOSFET] Vds = 1.0 

 Voltage
 I(typ)
 I(min)
 I(max)

 5.0V
 257.9m
 153.3m
 399.5m
 | Defines the Ids current as a

 4.0V
 203.0m
 119.4m
 317.3m
 | function of Vgs, for Vds = 1.0

 3.0V
 129.8m
 74.7m
 205.6m

 2.0V 31.2m 16.6m 51.Om 1.0V 52.7p 46.7p 56.7p 0.0p 0.0V 0.0p 0.0p \_\_\_\_\_ Keyword: [Ramp] Required: Yes, except for inputs, terminators, Series and Series\_switch model types. Description: Defines the rise and fall times of a buffer. The ramp rate does not include packaging but does include the effects of the C comp parameter. Sub-Params: dV/dt\_r, dV/dt\_f, R\_load Usage Rules: The rise and fall time is defined as the time it takes the output to go from 20% to 80% of its final value. The ramp rate is defined as: dV 20% to 80% voltage swing \_\_ \_ \_ \_\_\_\_ Time it takes to swing the above voltage dt The ramp rate must be specified as an explicit fraction and must not be reduced. The [Ramp] values can use "NA" for the min and max values only. The R\_load subparameter is optional if the default 50 ohm load is used. The R\_load subparameter is required if a non-standard load is used. \_\_\_\_\_ [Ramp] | variabletypminmaxdV/dt\_r2.20/1.06n1.92/1.28n2.49/650pdV/dt\_f2.46/1.21n2.21/1.54n2.70/770p  $R_load = 300$  ohms

Keywords:	[Rising Waveform], [Falling Waveform]
Required:	No
Description:	Describes the shape of the rising and falling edge waveforms of a driver.
Sub-Params:	R_fixture, V_fixture, V_fixture_min, V_fixture_max, C_fixture
Jsage Rules:	L_fixture, R_dut, L_dut, C_dut Each [Rising Waveform] and [Falling Waveform] keyword introduces a table of time vs. voltage points that describe the shape of an output waveform. These time/voltage points are taken under the conditions specified in the R/L/C/V_fixture and R/L/C_dut subparameters. The table itsel consists of one column of time points, then three columns of voltage points in the standard typ, min, and max format. The four entries must be placed on a single line and must be separated by at least one white space or tab character. All four columns are required. However, data is only required in the typical column. If minimum or maximum data is not available, use the reserved word "NA". The first value in th time column need not be '0'. Time values must increase as on parses down the table. The waveform table can contain a maximum of 100 data points. A maximum of 100 waveform tables are allowed per model. Note that for backward compatibility, the existing [Ramp] keyword is still required. The data in the waveform table is taken with the effects of the C_comp parameter included.
	A waveform table must include the entire waveform; i.e., the first entry (or entries) in a voltage column must be the DC voltage of the output before switching and the last entry (or entries) of the column must be the final DC value of the output after switching. Each table must contain at least two entries. Thus, numerical values are required for the first and last entries of any column containing numerical data.
	A [Model] specification can contain more than one rising edge or falling edge waveform table. However, each new table must begin with the appropriate keyword and subparameter list as shown below. If more than one rising or falling edge waveform table is present, then the data in each of the respective tables must be time correlated. In other words, the rising (falling) edge data in each of the rising (falling) edge waveform tables must be entered with respect to a common reference point on the input stimulus waveform.
	The 'fixture' subparameters specify the loading conditions under which the waveform is taken. The R_dut, C_dut, and L_dut subparameters are analogous to the package parameters R_pkg, C_pkg, and L_pkg and are used if the waveform includes the effects of pin inductance/capacitance. The diagram below shows the interconnection of these elements.

1.4000nS	2.1285V	1.3725V	3.0095V	
1.6000nS	2.3415V	1.5560V	3.1265V	
1.8000nS	2.5135V	1.7015V	3.1600V	
2.0000nS	2.6460V	1.8085V	3.1695V	
	2.7780V	2.3600V	3.1670V	
[Falling Wavefo	orm]			
$R_fixture = 50$				
$V_{fixture} = 5.5$	5			
V_fixture_min =	= 4.5			
V_fixture_max =	= 5.5			
Time	V(typ)	V(min)	V(max)	
0.0000S	5.0000V	4.5000V	5.5000V	
0.2000nS	4.7470V	4.4695V	4.8815V	
0.4000nS	3.9030V	4.0955V	3.5355V	
0.6000nS	2.7313V	3.4533V	1.7770V	
0.8000nS	1.8150V	2.8570V	0.8629V	
1.0000nS	1.1697V	2.3270V	0.5364V	
1.2000nS	0.7539V	1.8470V	0.4524V	
1.4000nS	0.5905V	1.5430V	0.4368V	
1.6000nS	0.4923V	1.2290V	0.4266V	
1.8000nS	0.4639V	0.9906V	0.4207V	
2.0000nS	0.4489V	0.8349V	0.4169V	
10.0000nS	0.3950V	0.4935V	0.3841V	
======================================				:==

\_\_\_\_\_

## Section 6a

ADD SUBMODEL DESCRIPTION

The [Add Submodel] keyword can be used under a top-level [Model] keyword to to add special-purpose functionality to the existing top-level model. This section describes the structure of the top-level model and the submodel.

TOP-LEVEL MODEL:

When special-purpose functional detail is needed, the top-level model can call one or more submodels. The [Add Submodel] keyword is positioned after the initial set of required and optional subparameters of the [Model] keyword and among the keywords under [Model].

The [Add Submodel] keyword lists of name of each submodel and the permitted mode (Driving, Non-Driving or All) under which each added submodel is used.

SUBMODEL:

A submodel is defined using the [Submodel] keyword. It contains a subset of keywords and subparameters used for the [Model] keyword along with other keywords and subparameters that are needed for the added functionality.

The [Submodel] and [Submodel Spec] keywords are defined first since they are used for all submodels

The only required subparameter in [Submodel] is Submodel\_type to define the list of submodel types. The other subparameters under [Model] are not permitted under the [Submodel] keyword.

The following set of keywords that are defined under the [Model] keyword are support by the [Submodel] keyword:

[Pulldown]
[Pullup]
[GND Clamp]
[POWER Clamp]
[Ramp]
[Rising Waveform]
[Falling Waveform]

The [Voltage Range], [Pullup Reference], [Pulldown Reference], [GND Clamp Reference], and [POWER Clamp Reference] keywords are not permitted. The voltage settings are inherited from the top-level model.

These additional keywords are used only for the [Submodel] are documented in this section:

[Submodel Spec] [GND Pulse Table]

[POWER Pulse Table] The application of these keywords depends upon the Submodel type entries listed below: Dynamic clamp Bus hold Permitted keywords that are not defined for any of these submodel types are ignored. Keyword: [Submodel] Required: No Description: Used to define a submodel, and its attributes. Sub-Params: Submodel type Usage Rules: Each submodel must begin with the keyword [Submodel]. The submodel name must match the one that is listed under the [Add Submodel] keyword and must not contain more than 20 characters. A .ibs file must contain enough [Submodel] keywords to cover all of the model names specified under the [Add Submodel] keyword. Submodel type subparameter is required and must be one of the following: Dynamic clamp, Bus hold The C\_comp subparameter is not permitted under the [Submodel] keyword. The total effective die capacitance including the submodel contributions are provided in the top-level model. Other Notes: The following list of keywords that are defined under the [Model] keyword can be used under [Submodel]: [Pulldown], [Pullup], [GND Clamp], [POWER Clamp], [Ramp], [Rising Waveform], and [Falling Waveform]. The following list of additional keywords can be used: [Submodel Spec], [GND Pulse Table], and [POWER Pulse Table]. | \_\_\_\_\_ [Submodel] Dynamic\_clamp1 Submodel\_type Dynamic\_clamp \_\_\_\_\_ Keyword: [Submodel Spec] Required: No Description: The [Submodel Spec] keyword defines four columns under which specification and information subparameters are defined for submodels. Sub-Params: V\_trigger\_r, V\_trigger\_f, Off\_delay Usage Rules: The [Submodel Spec] is to be used only with submodels. The following subparameters are used: V\_trigger\_r Rising edge trigger voltage Falling edge trigger voltage V\_trigger\_f

	Off_dela	У		off dela gger_f	y from V_trigger_r or
	remaining The entrie on a singl space or t the [Submo in the typ	three hold s of typic e line and ab charact del Spec] ical colum ble, the r	its typi al, minim must be er. All keyword. n. If mi reserved w	cal, min num and m separate four col However nimum an rord "NA"	e first column, the imum and maximum values. aximum be must be placed d by at least one white umns are required under , data is required only d/or maximum values are must be used to indicate
	The values in the minimum and maximum columns usually correspond to the values in the same columns for the inherited top-level voltage range or reference voltages in the top-level model. The V_trigger_r and V_trigger_f subparameters should hold values in the minimum and maximum columns that correspond to the voltage range or reference voltages of the top-level model. The Off_delay subparameter, however, is an exception to this rule because in some cases it may be completely or or partially independent from supply voltages and/or manufacturing process variations. Therefore the minimum and maximum entries for the Off_delay subparameter should be				
	ordered simply by their magnitude. Unless noted, each [Submodel Spec] subparameter is independent of any other subparameter.				
	V_trigger_r, V_trigger_f rules:				
		e starting			sing and falling edges ion is initiated.
	The functi	onality of			bparameter is to provide to turn off circuit
   Dynamic Clamp	Example:				
[Submodel Spec] Subparameter	c	typ	min	max	
 V_trigger_r V_trigger_f 		3.6 1.4	2.9 1.2	4.3   1.6	Starts power pulse table Starts gnd pulse table
   Bus Hold Examp	ple:				
 [Submodel Spec]   Subparameter V_trigger_r		typ 3.1	min 2.4 bus hold	max 3.7	Starts low to high
V_trigger_f		1.8	1.6 bus hold	2.0	Starts high to low

Bus\_hold application with pullup structure triggered on and then clocked off:

[Submodel Spec]						
Subparamete V_trigger_r	r typ 3.1	min 2.4	max 3.7   	Low to high transition triggers the turn on		
V_trigger_f	-10.0	-10.0	-10.0	process of the pullup Not used, so trigger voltages are set out		
Off_delay	5n	бn	4n   	of range Time from rising edge trigger at which the pullup turned off		
======================================						
Dynamic Clamp	:					
				nodel] keyword is set to clamp functionality.		
	e Table] and [PO complete dynami			ords are defined. An ded.		
	======================================			·		
<b>Keyword:</b> Required:	No	e], [POWER P	uise labie	= ]		
Description:	Used to specify the offset voltage versus time of [GND Clamp] and [POWER Clamp] tables within submodels.					
Usage Rules:	introduces a tal	ble of time '	versus vs.	se Table] keyword points that describe		
	the shape of an offset voltage from the [GND Clamp Reference] voltage (or default ground) or the [POWER Clamp Reference] voltage (or default [Voltage Range] voltage). Note, these voltage values are inherited from the top-level model.					
	The table itself consists of one column of time points, then three columns of voltage points in the standard typ, min, and max format. The four entries must be placed on a single line and must be separated by at least one white space or tab character. All four columns are required. However, data is only required in the typical column. If minimum or maximum data is not available, use the reserved word "NA". Time values must increase as one parses down the table. The waveform table can contain of maximum of 100 data points.					
	Each table must values are requ column containi:	ired for the	first and	entries. Thus, numerical a last entries of any		
	Pulse Table] tal instance, the [ Clamp] table vo At each instance	bles are dire Gnd Pulse Tal ltages to pro e, the [POWE]	ectly meas ble] volta ovide the R Pulse Ta	Pulse Table] and [POWER sured offsets. At each age is ADDED to the [GND shifted table voltages. able] voltage is entions) from the [POWER		

Clamp] table voltages to provide the shifted table voltages.

Only one [GND Pulse Table] and one [POWER Pulse Table] are allowed per model.

The [GND Pulse Table] and [POWER Pulse Table] interact with [Submodel Spec] subparameters V\_trigger\_f and V\_trigger\_r. Several modes of operation exist based on whether a pulse table and its corresponding trigger subparameter are given. These modes are classified as triggered and static.

Triggered Mode:

For triggered mode a pulse table must exist and include the entire waveform; i.e., the first entry (or entries) in a voltage column must be equal to the last entry.

Also, a corresponding [Submodel Spec] V\_trigger\_\* subparameter must exist. The triggered interaction is described:

The V\_trigger\_f subparameter under [Submodel Spec] is used to detect when the falling edge waveform at the die passes the trigger voltage. At that time the [Gnd Pulse Table] operation starts. Similarly, the V\_trigger\_r subparameter is used to detect when the rising edge waveform at the die passes the trigger voltage. At that time [POWER Pulse Table] operation starts. The [GND Pulse Table] dependency is shown below:



Waveform at Die

the V\_trigger\_r voltage value is reached on the rising edge, the [POWER

Pulse Table] is started. Normally the offset voltage entries in the [POWER Pulse Table] are negative. Static Mode: When the [GND Pulse Table] keyword does not exist, but the added model [GND Clamp] table does exist, the added model [GND Clamp] is used directly. Similarly, when the [POWER Pulse Table] keyword does not exist, but the added model [POWER Clamp] table does exist, the added model [POWER Clamp] is used directly. This mode provides additional fixed clamping to an I/O\_\* buffer or a 3-state buffer when it is used as a driver. Example of Dynamic\_clamp Model with both dynamic GND and POWER clamps: Dynamic\_Clamp\_1 [Submodel] Submodel\_type Dynamic\_clamp [Submodel Spec] Subparameter typ min max V\_trigger\_f 1.4 1.2 1.6 Falling edge trigger 4.3 | Rising edge trigger V\_trigger\_r 3.6 2.9 typ min max [Voltage Range] 5.0 4.5 5.5 Note, the actual voltage range and reference voltages are inherited from the top-level model. [GND Pulse Table] | GND Clamp offset table V(min) Time V(typ) V(max) 0 0 0 0 1e-9 0 0 0 0.8 2e-9 0.9 1.0 10e-9 0.9 0.8 1.0 11e-9 0 0 0 [GND Clamp] | Table to be offset Voltage I(typ) I(min) I(max) -5.000 -3.300e+01 -3.000e+01 -3.500e+01 -4.000-2.300e+01 -2.200e+01 -2.400e+01 -3.000 -1.300e+01 -1.200e+01 -1.400e+01 -2.000 -3.000e+00 -2.300e+00 -3.700e+00 -1.900 -2.100e+00 -1.500e+00 -2.800e+00 -1.800 -1.300e+00 -8.600e-01 -1.900e+00 -1.700-6.800e-01 -4.000e-01 -1.100e+00 -1.800e-01 -5.100e-01 -1.600 -2.800e-01 -1.200e-01 -1.800e-01 -1.500-9.800e-02 -1.400-7.500e-02 -7.100e-02 -8.300e-02 -1.300-5.750e-02 -5.700e-02 -5.900e-02 -1.200-4.600e-02 -4.650e-02 -4.550e-02 -1.100-3.550e-02 -3.700e-02 -3.450e-02

$\begin{array}{c} -1.000 \\ -0.900 \\ -0.800 \\ -0.700 \\ -0.600 \\ -0.500 \\ -0.400 \\ -0.300 \\ -0.200 \\ -0.100 \\ 0.000 \\ 5.000 \end{array}$	-2.650e-02 -1.850e-02 -1.200e-02 -6.700e-03 -3.000e-03 -9.450e-04 -5.700e-05 -1.200e-06 -3.000e-08 0.000e+00 0.000e+00 0.000e+00	-2.850e-02 -2.100e-02 -1.400e-02 -8.800e-03 -4.650e-03 -1.950e-03 -2.700e-04 -1.200e-05 -5.000e-07 0.000e+00 0.000e+00 0.000e+00	-2.500e-02 -1.650e-02 -9.750e-03 -4.700e-03 -1.600e-03 -3.650e-04 -5.550e-06 -5.500e-08 0.000e+00 0.000e+00 0.000e+00 0.000e+00	
 [POWER Pulse	Table]			POWER Clamp offset table
   Time	V(typ)	V(min)	V(max)	
0 1e-9 2e-9 10e-9 11e-9	0 0 -0.9 -0.9 0	0 0 -1.0 -1.0 0	0 0 -0.8 -0.8 0	
[POWER Clamp]				Table to be offset
   Voltage	I(typ)	I(min)	I(max)	
$\begin{array}{c} -5.000\\ -4.000\\ -3.000\\ -2.000\\ -1.900\\ -1.900\\ -1.800\\ -1.700\\ -1.600\\ -1.500\\ -1.500\\ -1.400\\ -1.300\\ -1.200\\ -1.100\\ -1.000\\ -0.900\\ -0.900\\ -0.800\\ -0.700\\ -0.600\\ -0.500\\ -0.500\\ -0.400\\ -0.300\\ -0.200\\ -0.100\end{array}$	1.150e+01 7.800e+00 4.350e+00 1.100e+00 8.000e-01 5.300e-01 1.200e-01 3.650e-02 1.200e-02 6.300e-03 4.200e-03 1.900e-03 1.900e-03 1.150e-03 5.500e-04 1.200e-04 5.400e-05 1.350e-05 8.650e-07 6.250e-08 0.000e+00 0.000e+00	1.100e+01 7.500e+00 4.100e+00 8.750e-01 6.050e-01 3.700e-01 1.800e-01 6.850e-02 2.400e-02 1.100e-02 6.650e-03 4.750e-03 3.500e-03 3.500e-03 9.150e-04 4.400e-04 1.550e-04 5.400e-05 7.450e-06 7.550e-07 8.400e-08 0.000e-08 0.000e+00	1.150e+01 8.150e+00 4.700e+00 1.300e+00 7.250e-01 4.500e-01 2.200e-01 6.900e-02 1.600e-02 6.100e-03 3.650e-03 2.350e-03 1.400e-03 7.100e-04 2.600e-04 5.600e-05 1.200e-05 1.300e-06 4.950e-08 0.000e+00 0.000e+00 0.000e+00	

Bus\_hold, the added model describes the bus hold functionality. However, while described in terms of bus hold functionality, active terminators can also be modeled.

Existing keywords and subparameters are used to describe bus hold models. The [Pullup] and [Pulldown] tables both are used to define an internal buffer that is triggered switch to its opposite state. This switching transition is specified by a [Ramp] keyword or by the [Rising Waveform] and [Falling Waveform] keywords. The usage rules for these keywords are the same as under the [Model] keyword. In particular, at least either the [Pullup] or [Pulldown] keyword is required. Also, the [Ramp] keyword is required, even if the [Rising Waveform] and [Falling Waveform] tables exist. However, the voltage ranges and reference voltages are inherited from the top-level model.

For bus hold submodels, the [Submodel Spec] keyword, V\_trigger\_r, and V\_trigger\_f are required. The Off\_delay subparameter is optional, but can only be used if the submodel consists of a pullup or a pulldown structure only, and not both. Devices which have both pullup and pulldown structures controlled in this fashion can be modeled using two submodels, one for each half of the circuit.

The transition is triggered by action at the die using the [Submodel Spec] V\_trigger\_r and V\_trigger\_f subparameters as follows:

If the starting voltage is below V\_trigger\_f, then the bus hold model is set to the low state causing additional pulldown current. If the starting voltage is above V\_trigger\_r, the bus hold model is set to the high state for additional pullup current. When the input passes though V\_trigger\_f during a high-to-low transition at the die, the bus hold output switches to the low state. Similarly, when the input passes though V\_trigger\_r during a low-to-high transition at the die, the bus hold output switches to the high state.

If the bus hold submodel has a pullup structure only, V\_trigger\_r provides the time when its pullup is turned on and V\_trigger\_f or Off\_delay provides the time when it is turned off, whichever occurs first. Similarly, if the submodel has a pulldown structure only, V\_trigger\_f provides the time when its pulldown is turned on and V\_trigger\_r or Off\_delay provides the time when it is turned off, whichever occurs first. The required V\_trigger\_r and V\_trigger\_f voltage entries can be set to values outside of the input signal range if the pullup or pulldown structures are to be held on until the Off\_delay turns them off.

The starting mode for each of the submodels which include the Off\_delay subparameter of the [Submodel Spec] keyword is the off state. Also, while two submodels provide the desired operation, either of the submodels may exist without the other to simulate turning on and off only a pullup or a pulldown current.

No additional keywords are needed for this functionality.

Complete Bus Hold Model Example:

[Submodel] Bus\_hold\_1 Submodel\_type Bus\_hold

	odel Spec] ubparameter		typ	min	max	
 V tric	gger_f		1.3	1.2	1.4	Falling edge trigger
	gger_r		3.1	2.6	4.6	Rising edge trigger
Note	ltage Range] e, the actua top-level m	l voltage	typ 5.0 range and	min 4.5 l reference	max 5.5 voltag	es are inherited from
   [Pullc		oder.				
		0.0 7	1007			
-5V -1V 0V 1V 3V 5V 10v	-100uA -30uA 0 30uA 50uA 100uA 120uA	-80uA -25uA 0 25uA 45uA 80uA 90uA	-120uA -40uA 0 40uA 50uA 120uA 150uA			
 [Pullu	ן קנ					
 -5V 0V 1V 3V 5V 10v	100uA 30uA 0 -30uA -50uA -100uA -120uA	80uA 25uA 0 -25uA -45uA -80uA -90uA				
   [Ramp]	]					
 dV/dt_ dV/dt_ R_load			p 0/0.50n 0/0.50n	min 2.0/0. 2.0/0.		max 2.0/0.35n 2.0/0.35n
       Comp   [Submo	plete Pullup		tch Exampl lup_latch	.e:		
	odel Spec]	Dab_nora				
	ubparameter		typ	min	max	
 V_trig	gger_r		3.1	2.6	4.6	Rising edge trigger   Values could be set ou   of range to disable th   trigger
V_trig Off_de	gger_f elay		1.3 3n	1.2 5n	1.4 2n	Falling edge trigger Delay to turn off the

1			_trigger_r value, the mer didn't expire yet.
[Voltage Range]   Note, the actual ve   the top-level mode	5.0 oltage range and	4.5 5	nax 5.5 oltages are inherited from
[Pulldown]			
 -5V -100uA - -1V -30uA - 0V 0 1V 30uA 3V 50uA 5V 100uA 10v 120uA     [Pullup] table is 0	25uA -40uA 0 0 25uA 40uA 45uA 50uA 80uA 120uA 90uA 150uA	l Open_source	e functionality
[Ramp]	typ	min	max
dV/dt_r			n 2.0/0.35n
dV/dt_f			n 2.0/0.35n
R_load = 500    =================================			

# **Section 7**

PACKAGE MODELING

\_\_\_\_\_ The [Package Model] keyword is optional. If more than the default RLC package model is desired, use the [Define Package Model] keyword. Use the [Package Model] keyword within a [Component] to indicate the package model for that component. The specification permits .ibs files to contain the following additional list of package model keywords. Note that the actual package models can be in a separate <package\_file\_name>.pkg file or can exist in the IBIS files between the [Define Package Model]... [End Package Model] keywords for each package model that is defined. For reference, these keywords are listed below. Full descriptions follow. Simulators that do not support these keywords will ignore all entries between the [Define Package Model] and [End Package Model] keywords. [Define Package Model] Required if the [Package Model] keyword is used [Manufacturer] (note 1) (note 1) [OEM] (note 1) [Description] [Number Of Sections] (note 2) [Number Of Pins] (note 1) [Pin Numbers] (note 1) [Model Data] (note 2) [Resistance Matrix] Optional when [Model Data] is used (note 3) [Inductance Matrix] [Capacitance Matrix] (note 3) [Bandwidth] Required (for Banded\_matrix matrices only) [Row] (note 3) [End Model Data] (note 2) [End Package Model] (note 1) (note 1) Required when the [Define Package Model] keyword is used (note 2) Either the [Number Of Sections] or the [Model Data]/[End Model Data] keywords are required. Note that [Number of Sections] and the [Model Data]/[End Model Data] keywords are mutually exclusive. (note 3) Required when the [Define Package Model] keyword is used and the [Number Of Sections] keyword is not used. When package model definitions occur within a .ibs file, their scope is "local" -- they are known only within that .ibs file and no other. In addition, within that .ibs file, they override any globally defined package models that have the same name. USAGE RULES FOR THE .PKG FILE: Package models are stored in a file whose name looks like: <filename>.pkg.

The <filename> provided must adhere to the General Syntax Rules. Use the ".pkg" extension to identify files containing package models. The .pkg file must contain all of the required elements of a normal .ibs file, including [IBIS Ver], [File Name], [File Rev], and the [End] keywords. Optional elements include the [Date], [Source], [Notes], [Disclaimer], [Copyright], and [Comment Char] keywords. All of the elements follow the same rules as those for a normal .ibs file. Note that the [Component] and [Model] keywords are not allowed in the .pkg file. The .pkg file is for package models only. \_\_\_\_\_ Keyword: [Define Package Model] Required: Yes Description: Marks the beginning of a package model description. Usage Rules: If the .pkg file contains data for more than one package, each section must begin with a new [Define Package Model] keyword. The length of the package model name must not exceed 40 characters in length. Blank characters are allowed. For every package model name defined under the [Package Model] keyword, there must be a matching [Define Package Model] keyword. \_\_\_\_\_ [Define Package Model] QS-SMT-cer-8-pin-pkqs Keyword: [Manufacturer] Required: Yes Description: Declares the manufacturer of the component(s) that use this package model. Usage Rules: The length of the manufacturer's name must not exceed 40 characters (blank characters are allowed, e.g., Texas Instruments). In addition, each manufacturer must use a consistent name in all .ibs and .pkg files. \_\_\_\_\_ [Manufacturer] Quality Semiconductors Ltd. \_\_\_\_\_ Keyword: [OEM] Required: Yes Description: Declares the manufacturer of the package. Usage Rules: The length of the manufacturer's name must not exceed 40 characters (blank characters are allowed). In addition, each manufacturer must use a consistent name in all .ibs and .pkg files. Other Notes: This keyword is useful if the semiconductor vendor sells a single IC in packages from different manufacturers. \_\_\_\_\_ [OEM] Acme Packaging Co. \_\_\_\_\_ Keyword: [Description] Required: Yes Description: Provides a concise yet easily human-readable description of what kind of package the [Package Model] is representing. Usage Rules: The description must be less than 60 characters in length,

must fit on a single line, and may contain spaces. \_\_\_\_\_ [Description] 220-Pin Quad Ceramic Flat Pack Keyword: [Number Of Sections] Required: No Description: Defines the maximum number of sections that make up a 'package stub'. A package stub is defined as the connection between the die pad and the corresponding package pin; it can include (but is not limited to) the bondwire, the connection between the bondwire and pin, and the pin itself. This keyword must be used if a modeler wishes to describe any package stub as other than a single, lumped L/R/C. The sections of a package stub are assumed to connect to each other in a series fashion. Usage Rules: The argument is a positive integer greater than zero. This keyword, if used, must appear in the specification before the [Pin Numbers] keyword. The maximum number of sections includes sections between the Fork and Endfork subparameters. \_\_\_\_\_ [Number Of Sections] 3 Keyword: [Number Of Pins] Required: Yes Description: Tells the parser how many pins to expect. Usage Rules: The field must be a positive decimal integer. The [Number Of Pins] keyword must be positioned before the [Pin Numbers] keyword. \_\_\_\_\_ [Number Of Pins] 128 Keyword: [Pin Numbers] Required: Yes Description: Tells the parser the set of names that are used for the package pins and also defines pin ordering. If the [Number Of Sections] keyword is present it also lists the elements for each section of a pin's die to pin connection. Sub-Params: Len, L, R, C, Fork, Endfork Usage Rules: Following the [Pin Numbers] keyword, the names of the pins are listed. There must be as many names listed as there are pins (as given by the preceding [Number Of Pins] keyword). Pin names can not exceed 5 characters in length. The first pin name given is the "lowest" pin, and the last pin given is the "highest." If the [Number Of Sections] keyword is used then each pin name must be followed by one or more of the legal subparameter combinations listed below. If the [Number Of Sections] keyword is not present then subparameter usage is NOT allowed. Subparameters: The Len, L, R, and C subparameters specify the length, inductance, capacitance and resistance of each section of each stub on a package.

The Fork and Endfork subparameters are used to denote branches from the main package stub.

Len The length of a package stub section. Lengths are given in terms of arbitrary 'units'.

L The inductance of a package stub section, in terms of 'inductance/unit length'. For example, if the total inductance of a section is 3.0nH and the length of the section is 2 'units', the inductance would be listed as L = 1.5nH (i.e. 3.0 / 2).

- C The capacitance of a package stub section, in terms of capacitance per unit length.
- R The DC (ohmic) resistance of a package stub section, in terms of ohms per unit length.
- Fork This subparameter indicates that the sections following (up to the Endfork subparameter) are part of a branch off of the main package stub. This subparameter has no arguments.
- Endfork This subparameter indicates the end point of a branch. For every Fork subparameter there must be a corresponding Endfork subparameter. As with the Fork subparameter, the Endfork subparameter has no arguments.

Specifying a Len or L/R/C value of zero is allowed. If Len = 0 is specified, then the L/R/C values are the total for that section. If a non-zero length is specified, then the total L/R/C for a section is calculated by multiplying the value of the Len subparameter by the value of the L, R, or C subparameter. However, if a non-zero length section is specified, the L and C for that section should be treated as distributed elements.

Using The Subparameters to Describe Package Stub Sections:

A section description begins with the Len subparameter and ends with the slash (/) character. The value of the Len, L, R, and C subparameters and the subparameter itself are separated by an equals sign (=); whitespace around the equals sign is optional. The Fork and Endfork subparameters are placed between section descriptions (i.e. between the concluding slash of one section and the 'Len' parameter that starts another). A particular section description can contain no data (i.e. the description is given as 'Len = 0 /').

Legal Subparameter Combinations for Section Descriptions:

A) A single Len = 0 subparameter, followed by a slash. This is used to describe a section with no data.

B) Len, and one or more of the L, R and C subparameters. If the Len subparameter is given as zero, then the L/R/C subparameters represent lumped elements. If the Len subparameter is non-zero, then the L/R/C subparameters represent distributed elements.

C) Single Fork or Endfork subparameter. Normally, a package

stub is described as several sections, with the Fork and EndFork subparameters surrounding a group of sections in the middle of the complete package stub description. However, it is legal for the Fork/Endfork subparameters to appear at the end of a section description. The package pin is connected to the last section of a package stub description not surrounded by a Fork/Endfork statements. See the examples below. Package Stub Boundaries: A package stub description starts at the connection to the die and ends at the point at which the package pin interfaces with the board or substrate the IC package is mounted on. Note that in the case of a component with thru-hole pins, the package stub description should include only the portion of the pin not physically inserted into the board or socket. However, it is legal for a package stub description to include both the component and socket together if this is how the component is intended to be used. A three-section package stub description that includes a bond wire (lumped inductance), a trace (treated as a transmission line with DC resistance), and a pin modeled as a lumped L/C element. [Pin Numbers] A1 Len=0 L=1.2n/ Len=1.2 L=2.0n C=0.5p R=0.05/ Len=0 L=2.0n C=1.0p/ Pin A2 below has a section with no data A2 Len=0 L=1.2n/ Len=0/ Len=1.2 L=2.0n C=0.5p R=0.05/ Len=0 L=2.0n C=1.0p/ A section description using the Fork and Endfork subparameters. Note that the indentation of the Fork and Endfork subparameters are for readability are not required. bondwire A1 Len=0 L=2.3n / Len=1.2 L=1.0n C=2.5p / | first section Fork | indicates the starting of a branch Len=1.0 L=2.0n C=1.5p /  $\mid$  section | ending of the branch Endfork second section Len=0.5 L=1.0 C=2.5p/ Len=0.0 L=1.5n / pin Here is an example where the Fork/Endfork subparameters are at the end of a package stub description B13 Len=0 L=2.3n / bondwire Len=1.2 L=1.0n C=2.5p / | first section second section, pin connects here Len=0.5 L=1.0 C=2.5/ indicates the starting of a branch Fork Len=1.0 L=2.0n C=1.5p / | section Endfork | ending of the branch Keyword: [Model Data] Required: Yes

Description: Indicates the beginning of the formatted package model data, that can include the [Resistance Matrix], [Inductance Matrix], [Capacitance Matrix], [Bandwidth], and [Row] keywords. \_\_\_\_\_ [Model Data] Keyword: [End Model Data] Required: Yes Description: Indicates the end of the formatted model data. Other Notes: In between the [Model Data] and [End Model Data] keywords is the package model data itself. The data is a set of 3 matrices: the resistance (R), inductance (L), and capacitance (C) matrices. Each matrix can be formatted differently (see below). Use one of the matrix keywords below to mark the beginning of each new matrix. \_\_\_\_\_ [End Model Data] Keywords: [Resistance Matrix], [Inductance Matrix], [Capacitance Matrix] Required: [Resistance Matrix] is optional. If it is not present, its entries are assumed to be zero. [Inductance Matrix] and [Capacitance Matrix] are required. Sub-Params: Banded\_matrix, Sparse\_matrix, or Full\_matrix Description: The subparameters mark the beginning of a matrix, and specify how the matrix data is formatted. Usage Rules: For each matrix keyword, use only one of the subparameters. After each of these subparameters, insert the matrix data in the appropriate format. (These formats are described in detail below.) Other Notes: The resistance, inductance, and capacitance matrices are also referred to as "RLC matrices" within this specification. When measuring the entries of the RLC matrices, either with laboratory equipment or field-solver software, currents are defined as ENTERING the pins of the package from the board (General Syntax Rule #11). The corresponding voltage drops are to be measured with the current pointing "in" to the "+" sign and "out" of the "-" sign. I1 +----+ I2 -----> | | <----board o----- Pkg |----- board + V1 - | | - V2 + +---+ It is important to observe this convention in order to get the correct signs for the mutual inductances and resistances. \_\_\_\_\_ [Resistance Matrix] Banded\_matrix [Inductance Matrix] Sparse\_matrix [Capacitance Matrix] Full matrix RLC MATRIX NOTES:

For each [Resistance Matrix], [Inductance Matrix], or [Capacitance Matrix] a different format can be used for the data. The choice of formats is provided to satisfy different simulation accuracy and speed requirements. Also, there are many packages in which the resistance matrix can have no coupling terms at all. In this case, the most concise format (Banded\_matrix) can be used.

There are two different ways to extract the coefficients that are reported in the capacitance and inductance matrices. For the purposes of this specification, the coefficients reported in the capacitance matrices shall be the 'electrostatic induction coefficients' or 'Maxwell's capacitances'. The Maxwell capacitance Kij is defined as the charge induced on conductor "j" when conductor "i" is held at 1 volt and all other conductors are held at zero volts. Note that Kij ( when i /= j) will be a negative number and should be entered as such. Likewise, for the inductance matrix the coefficients for Lij are defined as the voltage induced on conductor "j" when conductor "i"'s current is changed by lamp/sec and all other conductors have no current change.

One common aspect of all the different formats is that they exploit the symmetry of the matrices they describe. This means that the entries below the main diagonal of the matrix are identical to the corresponding entries above the main diagonal. Therefore, only roughly one-half of the matrix needs to be described. By convention, the main diagonal and the UPPER half of the matrix are provided.

In the following text, we use the notation [I, J] to refer to the entry in row I and column J of the matrix. Note that I and J are allowed to be alphanumeric strings as well as integers. An ordering of these strings is defined in the [Pin Numbers] section. In the following text, "Row 1" means the row corresponding to the first pin.

Also note that the numeric entries of the RLC matrices are standard IBIS floating point numbers. As such, it is permissible to use metric "suffix" notation. Thus, an entry of the C matrix could be given as 1.23e-12 or as 1.23p or 1.23pF.

Full\_matrix:

When the Full\_matrix format is used, the couplings between every pair of elements is specified explicitly. Assume that the matrix has N rows and N columns. The Full\_matrix is specified one row at a time, starting with Row 1 and continuing down to Row N.

Each new row is identified with the Row keyword.

Following a [Row] keyword is a block of numbers that represent the entries for that row. Suppose that the current row is number M. Then the first number listed is the diagonal entry, [M,M]. Following this number are the entries of the upper half of the matrix that belong to row M: [M, M+1], [M, M+2], ... up to [M,N]. For even a modest-sized package, this data will not all fit on one line. You can break the data up with new-line characters so that the 80 character line length limit is observed. An example: suppose the package has 40 pins and that we are currently working on Row 19. There is 1 diagonal entry, plus 40 - 19 = 21 entries in the upper half of the matrix to be specified, for 22 entries total. The data might be formatted as follows: [Row] 19 5.67e-9 1.1e-9 0.8e-9 0.6e-9 0.4e-9 0.2e-9 0.1e-9 0.09e-9 7e-10 6e-10 5e-10 4e-10 3e-10 2e-10 8e-10 1e-10 9e-11 8e-11 7e-11 6e-11 5e-11 4e-11 In the above example, the entry 5.67e-9 is on the diagonal of row 19. Observe that Row 1 always has the most entries, and that each successive row has one fewer entry than the last; the last row always has just a single entry. Banded matrix: A Banded\_matrix is one whose entries are guaranteed to be zero if they are farther away from the main diagonal than a certain distance, known as the "bandwidth." Let the matrix size be N x M, and let the bandwidth be B. An entry [I,J] of the matrix is zero if: | I - J | > B where |.| denotes the absolute value. The Banded\_matrix is used to specify the coupling effects up to B pins on either side. Two variations are supported. One allows for the coupling to circle back on itself. This is technically a simple form of a bordered block diagonal matrix. However, its data can be completely specified in terms of a Banded\_matrix for an N x M matrix consisting of N rows and M = N + B columns. The second variation is just in terms of an N x N matrix where no circle back coupling needs to be specified. The bandwidth for a Banded\_matrix must be specified using the [Bandwidth] keyword: \_\_\_\_\_ Keyword: [Bandwidth] Required: Yes (for Banded\_matrix matrices only) Description: Indicates the bandwidth of the matrix. Usage Rules: The bandwidth field must be a non-negative integer. This keyword must occur after the [Resistance Matrix], etc., keywords, and before the matrix data is given. \_\_\_\_\_ [Bandwidth] 10

### \_\_\_\_\_

Specify the banded matrix one row at a time, starting with row 1 and working up to higher rows. Mark each row with the [Row] keyword, as above. As before, symmetry is exploited: do not provide entries below the main diagonal.

For the case where coupling can circle back on itself, consider a matrix of N pins organized into N rows 1 ... N and M columns 1 ... N, 1 ... B. The first row only needs to specify the entries [1,1] through [1,1+B] since all other entries are guaranteed to be zero. The second row will need to specify the entries [2,2] through [2,2+B], and so on. For row K the entries [K,K] through [K,K+B] are given when K + B is less than or equal to the size of the matrix N. When K + B exceeds N, the entries in the last columns 1 ... B specify the coupling to the first rows. For row K, the entries [K,K] ... [K,N] [K,1] ... [K,R] are given where R = mod(K + B - 1, N) + 1. All rows will contain B + 1 entries. To avoid redundant entries, the bandwidth is limited to B <= int((N - 1) / 2).

For the case where coupling does not circle back on itself, the process is modified. Only N columns need to be considered. When K + B finally exceeds the size of the matrix N, the number of entries in each row starts to decrease; the last row (row N) has only 1 entry. This construction constrains the bandwidth to B < N.

As in the Full\_matrix, if all the entries for a particular row do not fit into a single 80-character line, the entries can be broken across several lines.

It is possible to use a bandwidth of 0 to specify a diagonal matrix (a matrix with no coupling terms.) This is sometimes useful for resistance matrices.

Sparse\_matrix:

A Sparse\_matrix is expected to consist mostly of zero-valued entries, except for a few nonzeros. Unlike the Banded\_matrix, there is no restriction on where the nonzero entries can occur. This feature is useful in certain situations, such as for Pin Grid Arrays (PGAs).

As usual, symmetry can be exploited to reduce the amount of data by eliminating from the matrix any entries below the main diagonal.

An N x N Sparse\_matrix is specified one row at a time, starting with row 1 and continuing down to row N. Each new row is marked with the [Row] keyword, as in the other matrix formats.

Data for the entries of a row is given in a slightly different format, however. For the entry [I, J] of a row, it is necessary to explicitly list the name of pin J before the value of the entry is given. This specification serves to indicate to the parser where the entry is put into the matrix.

The proper location is not otherwise obvious because of the lack of restrictions on where nonzeros can occur. Each (Index, Value) pair is listed upon a separate line. An example follows. Suppose that row 10 has nonzero entries [10,10], [10,11], [10,15], and [10,25]. The following row

data would be provided: [Row] 10 Index Value 10 5.7e-9 11 1.1e-9 15 1.1e-9 25 1.1e-9 Note that each of the column indices listed for any row must be greater than or equal to the row index, because they always come from the upper half of the matrix. When alphanumeric pin names are used, special care must be taken to ensure that the ordering defined in the [Pin Numbers] section is observed. With this convention, please note that the Nth row of an N x N matrix has just a single entry (the diagonal entry). Keyword: [End Package Model] Required: Yes Description: Marks the end of a package model description. Usage Rules: This keyword must come at the end of each complete package model description. Optionally, add a comment after the [End Package Model] keyword to clarify which package model has just ended. For example, [Define Package Model] My\_Model ... content of model ... [End Package Model] | end of My\_Model [End Package Model] Package Model Example The following is an example of a package model file following the package modeling specifications. For the sake of brevity, an 8-pin package has been described. For purposes of illustration, each of the matrices is specified using a different format. [IBIS Ver] 3.2 [File Name] example.pkg [File Rev] 0.1 [Date] January 15, 1999 [Source] Quality Semiconductors. Data derived from Helmholtz Inc.'s field solver using 3-D Autocad model from Acme Packaging. [Notes] Example of couplings in packaging [Disclaimer] The models given below may not represent any physically realizable 8-pin package. They are provided solely for the purpose of illustrating the .pkg file format.

```
[Define Package Model] QS-SMT-cer-8-pin-pkgs
                    Quality Semiconductors Ltd.
[Manufacturer]
[OEM]
                    Acme Package Co.
[Description]
                    8-Pin ceramic SMT package
[Number Of Pins]
                     8
[Pin Numbers]
1
2
3
4
5
б
7
8
[Model Data]
The resistance matrix for this package has no coupling
[Resistance Matrix]
                     Banded matrix
[Bandwidth]
                     0
[Row] 1
10.0
[Row]
       2
15.0
[Row]
       3
15.0
[Row]
       4
10.0
[Row]
       5
10.0
[Row] 6
15.0
[Row] 7
15.0
[Row]
       8
10.0
 The inductance matrix has loads of coupling
[Inductance Matrix]
                    Full_matrix
[Row] 1
3.04859e-07
              4.73185e-08
                             1.3428e-08
                                           6.12191e-09
1.74022e-07
               7.35469e-08
                             2.73201e-08
                                           1.33807e-08
[Row] 2
3.04859e-07
                             1.3428e-08
                                           7.35469e-08
               4.73185e-08
1.74022e-07
               7.35469e-08
                             2.73201e-08
[Row]
     3
3.04859e-07
               4.73185e-08
                             2.73201e-08
                                           7.35469e-08
1.74022e-07
               7.35469e-08
[Row]
     4
               1.33807e-08
                             2.73201e-08
                                           7.35469e-08
3.04859e-07
1.74022e-07
```

```
[Row] 5
4.70049e-07
                            5.75805e-08
                                          2.95088e-08
              1.43791e-07
[Row] 6
4.70049e-07
              1.43791e-07
                            5.75805e-08
[Row] 7
4.70049e-07
              1.43791e-07
[Row] 8
4.70049e-07
 The capacitance matrix has sparse coupling
[Capacitance Matrix]
                    Sparse_matrix
[Row]
      1
1
      2.48227e-10
2
      -1.56651e-11
5
      -9.54158e-11
6
      -7.15684e-12
[Row]
      2
     2.51798e-10
2
3
      -1.56552e-11
5
      -6.85199e-12
б
       -9.0486e-11
7
      -6.82003e-12
[Row]
      3
      2.51798e-10
3
4
      -1.56651e-11
6
      -6.82003e-12
7
       -9.0486e-11
8
      -6.85199e-12
      4
[Row]
4
      2.48227e-10
7
      -7.15684e-12
8
      -9.54158e-11
[Row]
      5
      1.73542e-10
5
      -3.38247e-11
6
[Row]
      6
      1.86833e-10
6
7
      -3.27226e-11
[Row] 7
7
      1.86833e-10
      -3.38247e-11
8
[Row]
      8
      1.73542e-10
8
[End Model Data]
[End Package Model]
```

#### \_\_\_\_\_

## **Section 8**

ELECTRICAL BOARD DESCRIPTION

A "board level component" is the generic term to be used to describe a printed circuit board (PCB) or substrate which can contain components or even other boards, and which can connect to another board through a set of user visible pins. The electrical connectivity of such a board level component is referred to as an "Electrical Board Description". For example, a SIMM module is a board level component that is used to attach several DRAM components on the PCB to another board through edge connector pins. An electrical board description file (a .ebd file) is defined to describe the connections of a board level component between the board pins and its components on the board.

A fundamental assumption regarding the electrical board description is that the inductance and capacitance parameters listed in the file are derived with respect to well-defined reference plane(s) within the board. Also, this current description does not allow one to describe electrical (inductive or capacitive) coupling between paths. It is recommended that if coupling is an issue, then an electrical description be extracted from the physical parameters of the board.

What is, and is not, included in an Electrical Board Description is defined by its boundaries. For the definition of the boundaries, see the Description section under the [Path Description] Keyword.

USAGE RULES:

A .ebd file is intended to be a stand-alone file, not associated with any .ibs file. Electrical Board Descriptions are stored in a file whose name looks like <filename>.ebd, where <filename> must conform to the naming rules given in the General Syntax Section of this specification. The .ebd extension is mandatory.

CONTENTS:

A .ebd file is structured similar to a standard IBIS file. It must contain the following keywords, as defined in the IBIS specification: [IBIS Ver], [File Name], [File Rev], and [End]. It may also contain the following optional keywords: [Comment Char], [Date], [Source], [Notes], [Disclaimer], and [Copyright]. The actual board description is contained between the keywords [Begin Board Description] and [End Board Description], and includes the keywords listed below:

[Begin Board Description] [Manufacturer] [Number Of Pins] [Pin List] [Path Description] [Reference Designator Map]

Description]
e [Begin Board Description]/[End Board Description] keyword pair a .ebd file.
[Begin Board Description] Yes
Marks the beginning of an Electrical Board Description. The keyword is followed by the name of the board level component. If the .ebd file contains more than one [Begin Board Description] keyword, then each name must be unique. The length of the component name must not exceed 40 characters in length, and blank characters are allowed. For every [Begin Board Description] keyword there must be a matching [End Board Description] keyword.
escription] 16Meg X 8 SIMM Module
[Manufacturer] Yes
Declares the manufacturer of the components(s) that use this .ebd file.
Following the keyword is the manufacturer's name. It must not exceed 40 characters, and can include blank characters. Each manufacturer must use a consistent name in all .ebd files.
Quality SIMM Corp.
[Number Of Pins]
Yes Tells the parser the number of pins to expect. Pins are any externally accessible electrical connection to the component.
The field must be a positive decimal integer. Note: The simulator must not limit the Number Of Pins to any value less than 1,000. The [Number Of Pins] keyword must be positioned before the [Pin List] keyword.
] 128
[Pin List] Yes
Tells the parser the pin names of the user accessible pins. It also informs the parser which pins are connected to power
and ground. signal_name Following the [Pin List] keyword are two columns. The first column lists the pin name while the second lists the data book name of the signal connected to that pin. There must be as many pin_name/signal_name rows as there are pins given by the preceding [Number Of Pins] keyword. Pin names must be the alphanumeric external pin names of the part. The pin names cannot exceed eight characters in length. Any pin associated

```
interpreted as connecting to the boards ground or power plane.
              In addition, NC is a legal signal name and indicates that the
              Pin is a 'no connect'. As per the IBIS standard "GND",
              "POWER" and "NC" are case insensitive.
_____
                                                       A SIMM Board Example
[Pin List] signal_name
A1
           GND
Α2
           data1
A3
           data2
Α4
           POWER5
                     | this pin connects to 5v
Α5
                     | a no connect pin
           NC
 •
 .
           POWER3.3 | this pin connects to 3.3v
A22
B1
           casa
 .
.
etc.
_____
     Keyword: [Path Description]
    Required:
              Yes
 Description: This keyword allows the user to describe the connection
              between the user accessible pins of a board level component
              and other pins or pins of the ICs mounted on that board. Each
              pin to node connection is divided into one or more cascaded
              "sections", where each section is described in terms of its
              L/R/C per unit length. The Fork and Endfork subparameters
              allow the path to branch to multiple nodes, or another pin. A
              path description is required for each pin whose signal name is
              not "GND", "POWER" or "NC".
              Board Description and IC Boundaries:
              In any system, each board level component interfaces with
              another board level component at some boundary. Every
              electrical board description must contain the components
              necessary to represent the behavior of the board level
              component being described within its boundaries. The boundary
              definition depends upon the board level component being
              described.
              For CARD EDGE CONNECTIONS such as a SIMM or a PC Daughter Card
              plugged into a SIMM Socket or Edge Connector, the boundary
              should be at the end of the board card edge pads as they
              emerge from the connector.
              For any THROUGH-HOLE MOUNTED COMPONENT, the boundary will be
              at the surface of the board on which the component is mounted.
              SURFACE MOUNTED COMPONENT models end at the outboard end of
              their recommended surface mount pads.
              If the board level component contains an UNMATED CONNECTOR,
              the unmated connector will be described in a separate file,
```

	with its boundaries being as described above for the through-hole or surface mounted component.
Sub-Params: Usage Rules:	Len, L, R, C, Fork, Endfork, Pin, Node Each individual connection path (user pin to node(s)) description begins with the [Path Description] keyword and a path name, followed by the subparameters used to describe the path topology and the electrical characteristics of each section of the path. The path name must not exceed 40 characters, blanks are not allowed, and each occurrence of the [Path Description] keyword must be followed by a unique path name. Every signal pin (pins other than POWER, GND or NC) must appear in one and only one path description per [Begin Board Description]/[End Board Description] pair. Pin names do not have to appear in the same order as listed in the [Pin List] table. The individual subparameters are broken up into those that describe the electrical properties of a section, and those that describe the topology of a path.
	Section Description Subparameters:
	The Len, L, R, and C subparameters specify the length, the series inductance, resistance, and the capacitance to ground of each section in a path description.
	Len The physical length of a section. Lengths are given in terms of arbitrary 'units'. Any non-zero length requires that the parameters that follow must be interpreted as distributed elements by the simulator. L The series inductance of a section, in terms of 'inductance/unit length'. For example, if the total inductance of a section is 3.0 nH and the length of the section is 2 'units', the inductance would be listed as L = 1.5 nH (i.e. 3.0 / 2). C The capacitance to ground of a section, in terms of capacitance per unit length. R The series DC (ohmic) resistance of a section, in terms of ohms per unit length.
	Topology Description Subparameters:
	The Fork and Endfork subparameters denote branches from the main pin-to-node or pin-to-pin connection path. The Node subparameter is used to reference the pin of a component or board as defined in a .ibs or .ebd file. The Pin subparameter is used to indicate the point at which a path connects to a user visible pin.
	<ul><li>Fork This subparameter indicates that the sections following (up to the Endfork subparameter) are part of a branch off of the main connection path. This subparameter has no arguments.</li><li>Endfork This subparameter indicates the end point of a branch. For every Fork subparameter there must be a</li></ul>
	corresponding Endfork subparameter. As with the Fork subparameter, the Endfork subparameter has no arguments. The Fork and Endfork parameters must

Node

appear on separate lines.

reference\_designator.pin This subparameter is used when the connection path connects to a pin of another, externally defined component. The arguments of the Node subparameter indicate the pin and reference designator of the external component. The pin and reference designator portions of the argument are separated by a period ("."). The reference designator is mapped to an external component description (another .ebd file or .ibs file) by the [Reference Designator Map] Keyword. Note that a Node MUST reference a model of a passive or active component. A Node is not an arbitrary connection point between two elements or paths. Pin This subparameter is used to mark the point at which a path description connects to a user accessible pin. Every path description must contain at least one occurrence of the Pin subparameter. It may also contain the reserved word NC. The value of the Pin subparameter must be one of the pin names listed in the [Pin List] section.

Note: The reserved word NC can also be used in path descriptions in a similar manner as the subparameters in order to terminate paths. This usage is optional.

Using The Subparameters to Describe Paths:

A section description begins with the Len subparameter and ends with the slash (/) character. The value of the Len, L,  $R\,,$  and C subparameters and the subparameter itself are separated by an equals sign (=); whitespace around the equals sign is optional. The Fork, Endfork, Node and Pin subparameters are placed between section descriptions (i.e., between the concluding slash of one section and the 'Len' parameters that starts another). The arguments of the Pin and Node subparameter are separated by white space.

Specifying a Len or L/R/C value of zero is allowed. If Len = 0 is specified, then the L/R/C values are the total for that section. If a non-zero length is specified, then the total L/R/C for a section is calculated by multiplying the value of the Len subparameter by the value of the L, R, or C subparameter. However, as noted below, if a non-zero length is specified, that section MUST be interpreted as distributed elements.

Legal Subparameter Combinations for Section Descriptions:

A) Len, and one or more of the L, R and C subparameters. Ιf the Len subparameter is given as zero, then the L/R/Csubparameters represent lumped elements. If the Len subparameter is non-zero, then the L/R/C subparameters represent distributed elements and both L and C must be specified, R is optional. The segment Len ..../ must not be split; the whole segment must be on one line.

```
B) The first subparameter following the [Path Description]
               keyword must be 'Pin', followed by one or more section
               descriptions. The path description can terminate in a Node,
               another pin or the reserved word, NC. However, NC may be
               optionally omitted.
               Dealing With Series Elements:
               A discrete series R or L component can be included in a path
               description by defining a section with Len=0 and the proper R
               or L value. A discrete series component can also be included
               in a path description by writing two back to back node
               statements that reference the same component (see the example
               below).
                        Note that both ends of a discrete, two terminal
               component MUST be contained in a single [Path Description].
               Connecting two separate [Path Description]s with a series
               component is not allowed.
                                               _____
   An Example Path For a SIMM Module:
[Path Description] CAS_2
Pin J25
Len = 0.5 L=8.35n C=3.34p R=0.01 /
Node u21.15
Len = 0.5 \text{ L}=8.35n \text{ C}=3.34p \text{ R}=0.01 /
Node u22.15
Len = 0.5 \text{ L}=8.35n \text{ C}=3.34p \text{ R}=0.01 /
Node u23.15
   A Description Using The Fork and Endfork Subparameters:
[Path Description] PassThrul
Pin B5
Len = 0
        L=2.0n /
Len = 2.1 L=6.0n C=2.0p /
Fork
Len = 1.0 L = 1.0n C = 2.0p /
Node u23.15
Endfork
Len = 1.0 L = 6.0n C = 2.0p /
Pin A5
   A Description Including a Discrete Series Element:
[Path Description] sig1
Pin B27
Len = 0 L=1.6n /
Len = 1.5 \text{ L}=6.0n \text{ C}=2.0p /
Node R2.1
Node R2.2
Len = 0.25 L=6.0n C=2.0p /
Node U25.6
```

Keyword: Required: Description: Usage Rules:	[Reference Designator Map] Yes, if any of the path descriptions use the Node subparameter Maps a reference designator to a component or electrical board description contained in an .ibs or .ebd file. The [Reference Designator Map] keyword must be followed by a list of all of the reference designators called out by the Node subparameters used in the various path descriptions. Each reference designator is followed by the name of the .ibs or .ebd file containing the electrical description of the component or board, then the name of the component itself as given by the .ibs or .ebd file's [Component] or [Begin Board Description] keyword respectively. The reference designator, file name and component name terms are separated by whitespace. By default the .ibs or .ebd files are assumed to exist in the same directory as the calling .ebd file. It is legal for a reference designator to point to a component that is contained in the calling .ebd file.
 	The reference designator is limited to ten characters.
Reference Desi	gnator Map]
External Par	t References:
124 simm 125 ls24 126 r10K	0.ibs Pentium(R)Pro_Processor a.ebd 16Meg X 36 SIMM Module 4.ibs National 74LS244a 5.ibs My_10K_Pullup
=====================================	[End Board Description]
Required: Description: Usage Rules:	Yes Marks the end of an Electrical Interconnect Description. This keyword must come at the end of each complete electrical interconnect model description.
	Optionally, a comment may be added after the [End Electrical Description] keyword to clarify which board model has ended.
 [End Board Desc	ription]   End: 16Meg X 8 SIMM Module
   ===================================	
Keyword: Required: Description:	<b>[End]</b> Yes Defines the end of the .ibs, .pkg, or .ebd file.
 [End]	
===============	

#### \_\_\_\_\_

### Section 9

NOTES ON DATA DERIVATION METHOD

This section explains how data values are derived. It describes certain assumed parameter and table extraction conditions if they are not explicitly specified. It also describes the allocation of data into the "typ", "min", and "max" columns under variations of voltage, temperature, and process.

The required "typ" column for all data represents typical operating conditions. For most [Model] keyword data, the "min" column describes slow, weak performance, and the "max" column describes the fast, strong performance. It is permissible to use slow, weak components or models to derive the data for the "min" column, and to use fast, strong components or models to derive the data in the "max" columns under the corresponding voltage and temperature derating conditions for these columns. It is also permissible to use typical components or models derated by voltage and temperature and optionally apply proprietary "X%" and "Y%" factors described later for further derating. This methodology has the nice feature that the data can be derived either from semiconductor vendor proprietary models, or typical component measurement over temperature/voltage.

The voltage and temperature keywords and optionally the process models control the conditions that define the "typ", "min", and "max" column entries for all V/I table keywords [Pulldown], [Pullup], [GND Clamp], and [POWER Clamp]; all [Ramp] subparameters dV/dt\_r and dV/dt\_f; and all waveform table keywords and subparameters [Rising Waveform], [Falling Waveform], V\_fixture, V\_fixture\_min, and V\_fixture\_max.

The voltage keywords that control the voltage conditions are [Voltage Range], [Pulldown Reference], [Pullup Reference], [GND Clamp Reference], and [POWER Clamp Reference]. The entries in the "min" columns contain the smallest magnitude voltages, and the entries in the "max" columns contain the largest magnitude voltages.

The optional [Temperature Range] keyword will contain the temperature which causes or amplifies the slow, weak conditions in the "min" column and the temperature which causes or amplifies the fast, strong conditions in the "max" column. Therefore, the "min" column for [Temperature Range] will contain the lowest value for bipolar models (TTL and ECL) and the highest value for CMOS models. Default values described later are assumed if temperature is not specified.

The "min" and "max" columns for all remaining keywords and subparameters will contain the smallest and largest magnitude values. This applies to the [Model] subparameter C\_comp as well even if the correlation to the voltage, temperature, and process variations are known because information about such correlation is not available in all cases.

C\_comp is considered an independent variable. This is because C\_comp includes bonding pad capacitance, which does not necessarily track

fabrication process variations. The conservative approach to using IBIS data will associate large C\_comp values with slow, weak models, and the small C\_comp values with fast, strong models."

The default temperatures under which all V/I tables are extracted are provided below. The same defaults also are stated for the [Ramp] subparameters, but they also apply for the waveform keywords.

The stated voltage ranges for V/I tables cover the most common, single supply cases. When multiple supplies are specified, the voltages shall extend similarly to values that handle practical extremes in reflected wave simulations.

For the [Ramp] subparameters, the default test load and voltages are provided. However, the test load can be entered directly by the R\_load subparameter. The allowable test loads and voltages for the waveform keywords are stated by required and optional subparameters; no defaults are needed. Even with waveform keywords, the [Ramp] keyword continues to be required so that the IBIS model remains functional in situations which do not support waveform processing.

The following discussion lists test details and default conditions.

### 1) V/I tables for CMOS models:

typ = typical voltage, typical temp deg C, typical process min = minimum voltage, max temp deg C, typical process, minus "X%" max = maximum voltage, min temp deg C, typical process, plus "X%"

V/I tables for bipolar models:

typ = typical voltage, typical temp deg C, typical process min = minimum voltage, min temp deg C, typical process, minus "X%" max = maximum voltage, max temp deg C, typical process, plus "X%"

Nominal, min, and max temperature are specified by the semiconductor vendor. The default range is 50 deg C nom, 0 deg C min, and 100 deg C max temperatures.

X% should be statistically determined by the semiconductor vendor based on numerous fab lots, test chips, process controls, etc.. The value of X need not be published in the IBIS file, and may decrease over time as data on the I/O buffers and silicon process increases.

Temperatures are junction temperatures.

### 2) Voltage Ranges:

Points for each table must span the voltages listed below:

Table	Low Voltage	High Voltage
[Pulldown]	GND - POWER	POWER + POWER
[Pullup]	GND - POWER	POWER + POWER
[GND Clamp]	GND - POWER	GND + POWER
[POWER Clamp]	POWER	POWER + POWER
[Series Current]	GND - POWER	GND + POWER
[Series MOSFET]	GND	GND + POWER

As described in the [Pulldown Reference] keyword section, the V/I tables

of the [Pullup] and the [POWER Clamp] structures are 'Vcc relative', using the equation: Vtable = Vcc - Voutput.

For example, a model with a 5 V power supply voltage should be characterized between (0 - 5) = -5 V and (5 + 5) = 10 V; and a model with a 3.3 V power supply should be characterized between (0 - 3.3) = -3.3 V and (3.3 + 3.3) = 6.6 V for the [Pulldown] table.

When tabulating output data for ECL type models, the voltage points must span the range of Vcc to Vcc - 2.2 V. This range applies to both the [Pullup] and [Pulldown] tables. Note that this range applies ONLY when characterizing an ECL output.

These voltage ranges must be spanned by the IBIS data. Data derived from lab measurements may not be able to span these ranges as such and so may need to be extrapolated to cover the full range. This data must not be left for the simulator to provide.

### 3) Ramp Rates:

The following steps assume that the default load resistance of 50 ohms is used. There may be models that will not drive a load of only 50 ohms into any useful level of dynamics. In these cases, use the semiconductor vendor's suggested (nonreactive) load and add the load subparameter to the [Ramp] specification.

The ramp rate does not include packaging but does include the effects of the C\_comp parameter; it is the intrinsic output stage rise and fall time only.

The ramp rates (listed in AC characteristics below) should be derived as follows:

- a. If starting with the silicon model, remove all packaging. If starting with a packaged model, perform the measurements as outlined below.
   Then use whatever techniques are appropriate to derive the actual, unloaded rise and fall times.
- b. If: The Model\_type is one of the following: Output, I/O, or 3-state (not open or ECL types);
  Then: Attach a 50 ohm resistor to GND to derive the rising edge ramp. Attach a 50 ohm resistor to POWER to derive the falling edge ramp.
  - If: The Model\_type is Output\_ECL, I/O\_ECL, 3-state\_ECL; Then: Attach a 50 ohm resistor to the termination voltage (Vterm = VCC - 2 V). Use this load to derive both the rising and falling edges.
  - If: The Model\_type is either an Open\_sink type or Open\_drain type; Then: Attach either a 50 ohm resistor or the semiconductor vendor suggested termination resistance to either POWER or the suggested termination voltage. Use this load to derive both the rising and falling edges.
  - If: The Model\_type is an Open\_source type; Then: Attach either a 50 ohm resistor or the semiconductor vendor suggested termination resistance to either GND or the

suggested termination voltage. Use this load to derive both the rising and falling edges.

- c. Due to the resistor, output swings will not make a full transition as expected. However the pertinent data can still be collected as follows:
  - 1) Determine the 20% to 80% voltages of the 50 ohm swing.
  - 2) Measure this voltage change as "dV".
  - 3) Measure the amount of time required to make this swing "dt".
- d. Post the value as a ratio "dV/dt". The simulator extrapolates this value to span the required voltage swing range in the final model.
- e. Typ, Min, and Max must all be posted, and are derived at the same extremes as the V/I tables, which are:

Ramp rates for CMOS models:

typ = typical voltage, typical temp deg C, typical process min = minimum voltage, max temp deg C, typical process, minus "Y%" max = maximum voltage, min temp deg C, typical process, plus "Y%"

Ramp rates for bipolar models:

typ = typical voltage, typical temp deg C, typical process min = minimum voltage, min temp deg C, typical process, minus "Y%" max = maximum voltage, max temp deg C, typical process, plus "Y%"

where nominal, min, and max temp are specified by the semiconductor vendor. The preferred range is 50 deg C nom, 0 deg C min, and 100 deg C max temperatures.

Note that the derate factor, "Y%", may be different than that used for the V/I table data. This factor is similar to the X% factor described above. As in the case of V/I tables, temperatures are junction temperatures.

f. During the IV measurements, the driving waveform should have a rise/fall time fast enough to avoid thermal feedback. The specific choice of sweep time is left to the modeling engineer.

### 4) Transit Time Extractions:

The transit time parameter is indirectly derived to be the value that produces the same effect as that extracted by the reference measurement or reference simulation.

The test circuit consists of the following:

- a) A pulse source (10 ohms, 1 ns at full duration ramp) or equivalent and transitioning between Vcc and 0 V,
- b) A 50 ohm, 1 ns long trace or transmission line,
- c) A 500 ohm termination to the ground clamp reference voltage for TTgnd extraction and to the power clamp reference voltage for TTpower extraction (to provide a convenient, minimum loading 450 ohm - 50 ohm divider for high-speed sampling equipment observation of the component denoted as the device under test), and
- d) The device under test (DUT).



Example of TTgnd Extraction Setup

The TTgnd extraction will be done only if a [GND Clamp] table exists. A high to low transition that produces a positive "glitch", perhaps several nanoseconds later indicates a stored charge in the ground clamp circuit. The test circuit is simulated using the complete IBIS model with C\_comp and the Ct model defined under the [TTgnd] and [TTpower] keywords. An effective TTgnd value that produces a "glitch" with the same delay is extracted.

Similarly, the TTpower extraction will be done only if a [POWER Clamp] table exists. A low to high transition that produces a negative "glitch", perhaps several nanoseconds later indicates a stored charge in the power clamp circuit. An effective TTpower value that produces a glitch with the same delay is extracted.

It is preferred to do the extractions with the package parameters removed. However, if the extraction is done from measurements, then the package model should be included in the IBIS based simulation.

### 5) Series MOSFET Table Extractions:

An extraction circuit is set up according to the figure below. The switch is configured into the 'On' state. This assumes that the Vcc voltage will be applied to the gate by internal logic. Designate one pin of the switch as the source node, and the other pin as the drain node. The Table Currents designated as Ids are derived directly as a function of the Vs voltage at the source node as Vs is varied from 0 to Vcc. This voltage is entered as a Vgs value as a consequence of the relationship Vtable = Vgs = Vcc - Vs. Vds is held constant by having a fixed voltage Vds between the drain and source nodes. Note, Vds > 0 V. The current flowing into the drain is tabulated in the table for the corresponding Vs points.

